25 Flexible static memory controller (FSMC)

25.1 Introduction

The flexible static memory controller (FSMC) includes two memory controllers:

- The NOR/PSRAM memory controller
- The NAND memory controller

This memory controller is also named flexible memory controller (FMC).

25.2 FMC main features

The FMC functional block makes the interface with: synchronous and asynchronous static memories, and NAND Flash memory. Its main purposes are:

- to translate AHB transactions into the appropriate external device protocol
- to meet the access time requirements of the external memory devices

All external memories share the addresses, data and control signals with the controller. Each external device is accessed by means of a unique chip select. The FMC performs only one access at a time to an external device.

The main features of the FMC controller are the following:

- Interface with static-memory mapped devices including:
  - Static random access memory (SRAM)
  - NOR Flash memory/OneNAND Flash memory
  - PSRAM (4 memory banks)
  - Ferroelectric RAM (FRAM)
  - NAND Flash memory with ECC hardware to check up to 8 Kbytes of data
- Interface with parallel LCD modules, supporting Intel 8080 and Motorola 6800 modes.
- Burst mode support for faster access to synchronous devices such as NOR Flash memory, PSRAM)
- Programmable continuous clock output for asynchronous and synchronous accesses
- 8-,16-bit wide data bus
- Independent chip select control for each memory bank
- Independent configuration for each memory bank
- Write enable and byte lane select outputs for use with PSRAM, SRAM devices
- External asynchronous wait control
- Write FIFO with 16 x32-bit depth

The Write FIFO is common to all memory controllers and consists of:

- a Write Data FIFO which stores the AHB data to be written to the memory (up to 32 bits) plus one bit for the AHB transfer (burst or not sequential mode)
- a Write Address FIFO which stores the AHB address (up to 28 bits) plus the AHB data size (up to 2 bits). When operating in burst mode, only the start address is stored except when crossing a page boundary (for PSRAM). In this case, the AHB burst is broken into two FIFO entries.

At startup the FMC pins must be configured by the user application. The FMC I/O pins which are not used by the application can be used for other purposes.

The FMC registers that define the external device type and associated characteristics are usually set at boot time and do not change until the next reset or power-up.

However, only a few bits can be changed on-the-fly:

- MBKEN, FMCEN, WEN bits in FMC_BCRx register
- ECCEN and PBKEN bits in the FMC_PCR register
- IFS, IRS and ILS bits in the FMC_SR register

Follow the below sequence to modify parameters while the FMC is enabled:

1. First disable the FMC controller to prevent further accesses to any memory controller while the register is modified.
2. Update all required configurations.
3. Enable the FMC controller again.

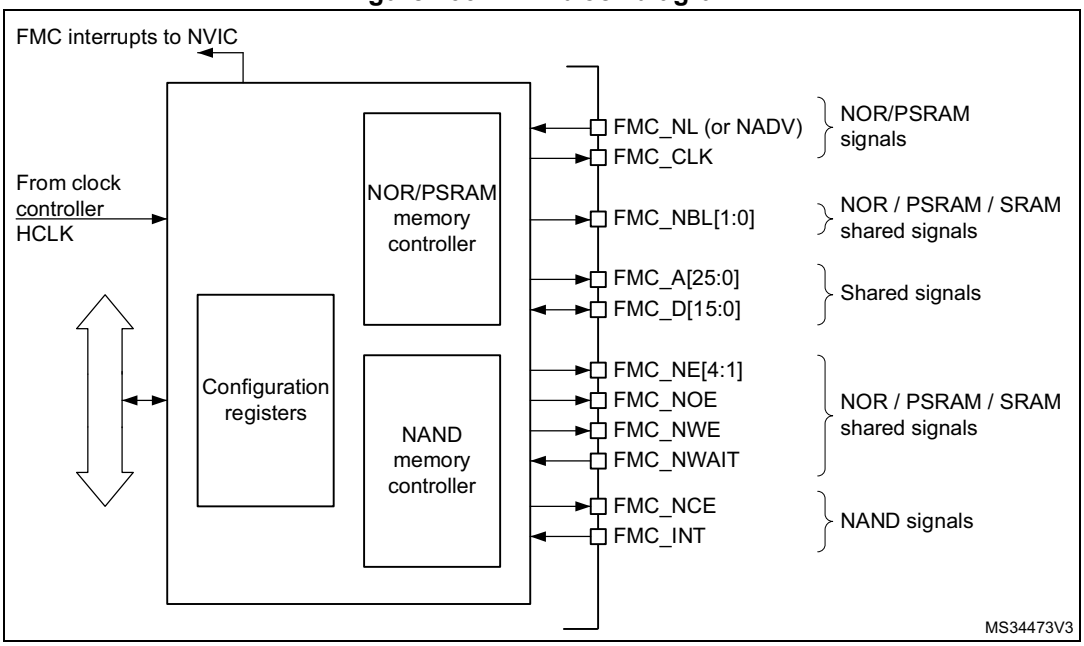
25.3 FMC block diagram

The FMC consists of the following main blocks:

- The AHB interface (including the FMC configuration registers)
- The NOR Flash/PSRAM/SRAM controller

The block diagram is shown in the figure below.

Figure 106. FMC block diagram



25.4 AHB interface

The AHB slave interface allows internal CPUs and other bus master peripherals to access the external memories.

AHB transactions are translated into the external device protocol. In particular, if the selected external memory is 16- or 8-bit wide, 32-bit wide transactions on the AHB are split into consecutive 16- or 8-bit accesses. The FMC chip select (FMC_NEx) does not toggle between the consecutive accesses except in case of Access mode D when the Extended mode is enabled.

The FMC generates an AHB error in the following conditions:

- When reading or writing to a FMC bank (Bank 1 to 4) which is not enabled.
- When reading or writing to the NOR Flash bank while the FACCEN bit is reset in the FMC_BCRx register.

The effect of an AHB error depends on the AHB master which has attempted the R/W access:

- If the access has been attempted by the Cortex®-M33 CPU, a hard fault interrupt is generated.
- If the access has been performed by a DMA controller, a DMA transfer error is generated and the corresponding DMA channel is automatically disabled.

The AHB clock (HCLK) is the reference clock for the FMC.

25.4.1 Supported memories and transactions

General transaction rules

The requested AHB transaction data size can be 8-, 16- or 32-bit wide whereas the accessed external device has a fixed data width. This may lead to inconsistent transfers.

Therefore, some simple transaction rules must be followed:

- AHB transaction size and memory data size are equal

  There is no issue in this case.
- AHB transaction size is greater than the memory size:

  In this case, the FMC splits the AHB transaction into smaller consecutive memory accesses to meet the external data width. The FMC chip select (FMC_NEx) does not toggle between the consecutive accesses. If the bus turnaround timings is configured to any other value than 0, the FMC chip select (FMC_NEx) toggles between the consecutive accesses. This feature is required when interfacing with FRAM memory.
- AHB transaction size is smaller than the memory size:

  The transfer may or not be consistent depending on the type of external device:
  - Accesses to devices that have the byte select feature (SRAM, ROM, PSRAM)

    In this case, the FMC allows read/write transactions and accesses the right data through its byte lanes NBL[1:0].

    Bytes to be written are addressed by NBL[1:0].

    All memory bytes are read (NBL[1:0] are driven low during read transaction) and the useless ones are discarded.

– Accesses to devices that do not have the byte select feature (NOR and NAND Flash memories)

This situation occurs when a byte access is requested to a 16-bit wide Flash memory. Since the device cannot be accessed in Byte mode (only 16-bit words can be read/written from/to the Flash memory), Write transactions and Read transactions are allowed (the controller reads the entire 16-bit memory word and uses only the required byte).

Wrap support for NOR Flash/PSRAM

Wrap burst mode for synchronous memories is not supported. The memories must be configured in Linear burst mode of undefined length.

Configuration registers

The FMC can be configured through a set of registers. Refer to *Section 25.6.6*, for a detailed description of the NOR Flash/PSRAM controller registers. Refer to *Section 25.7.7*, for a detailed description of the NAND Flash registers.

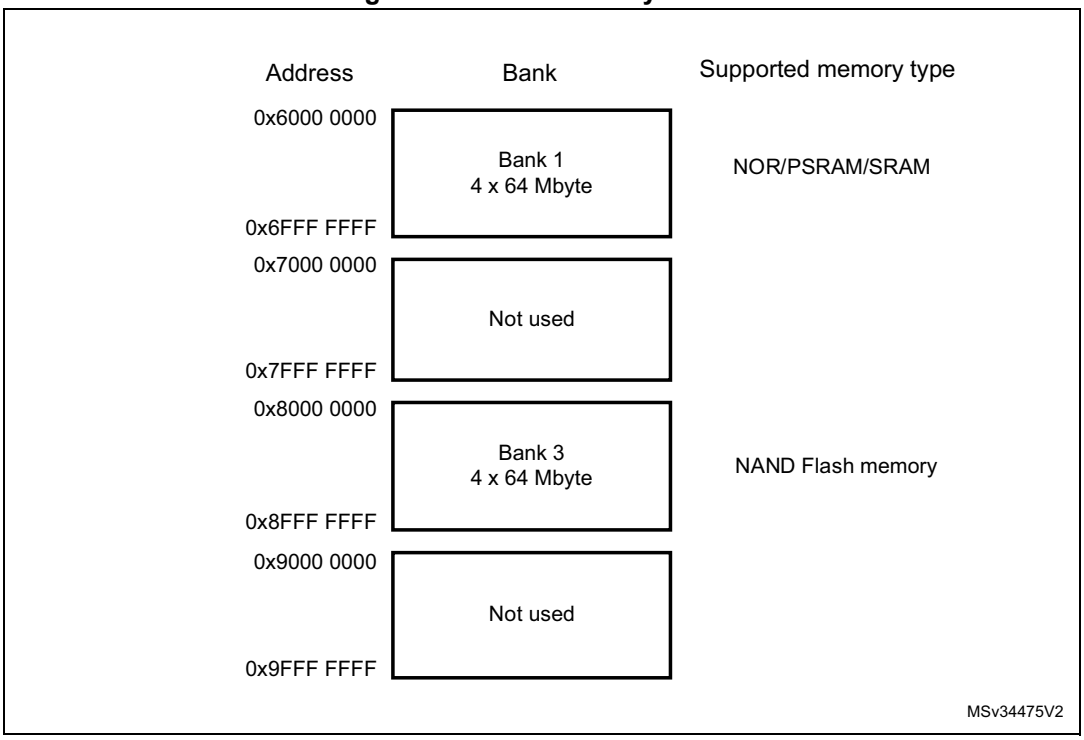
25.5 External device address mapping

From the FMC point of view, the external memory is divided into fixed-size banks of 256 Mbytes each (see *Figure 107*):

- Bank 1 used to address up to 4 NOR Flash memory or PSRAM devices. This bank is split into 4 NOR/PSRAM subbanks with 4 dedicated chip selects, as follows:
  - Bank 1 - NOR/PSRAM 1
  - Bank 1 - NOR/PSRAM 2
  - Bank 1 - NOR/PSRAM 3
  - Bank 1 - NOR/PSRAM 4
- Bank 3 used to address NAND Flash memory devices.The MPU memory attribute for this space must be reconfigured by software to Device.

For each bank the type of memory to be used can be configured by the user application through the Configuration register.

Figure 107. FMC memory banks



25.5.1 NOR/PSRAM address mapping

HADDR[27:26] bits are used to select one of the four memory banks as shown in *Table 180*.

Table 180. NOR/PSRAM bank selection

HADDR[27:26](1)	Selected bank
00	Bank 1 - NOR/PSRAM 1
01	Bank 1 - NOR/PSRAM 2
10	Bank 1 - NOR/PSRAM 3
11	Bank 1 - NOR/PSRAM 4

1. HADDR are internal AHB address lines that are translated to external memory.

The HADDR[25:0] bits contain the external memory address. Since HADDR is a byte address whereas the memory is addressed at word level, the address actually issued to the memory varies according to the memory data width, as shown in the following table.

Table 181. NOR/PSRAM External memory address

Memory width(1)	Data address issued to the memory	Maximum memory capacity (bits)
8-bit	HADDR[25:0]	64 Mbytes x 8 = 512 Mbits
16-bit	HADDR[25:1] >> 1	64 Mbytes/2 x 16 = 512 Mbits

1. In case of a 16-bit external memory width, the FMC internally uses HADDR[25:1] to generate the address for external memory FMC_A[24:0].
Whatever the external memory width, FMC_A[0] should be connected to external memory address A[0].

25.5.2 NAND Flash memory address mapping

The NAND bank is divided into memory areas as indicated in *Table 182*.

Table 182. NAND memory mapping and timing registers

Start address	End address	FMC bank	Memory space	Timing register
0x8800 0000	0x8BFF FFFF	Bank 3 - NAND Flash	Attribute	FMC_PATT (0x8C)
0x8000 0000	0x83FF FFFF		Common	FMC_PMEM (0x88)

For NAND Flash memory, the common and attribute memory spaces are subdivided into three sections (see in *Table 183* below) located in the lower 256 Kbytes:

- Data section (first 64 Kbytes in the common/attribute memory space)
- Command section (second 64 Kbytes in the common / attribute memory space)
- Address section (next 128 Kbytes in the common / attribute memory space)

Table 183. NAND bank selection

Section name	HADDR[17:16]	Address range
Address section	1X	0x020000-0x03FFFF
Command section	01	0x010000-0x01FFFF
Data section	00	0x000000-0x0FFFF

The application software uses the 3 sections to access the NAND Flash memory:

- **To sending a command to NAND Flash memory**, the software must write the command value to any memory location in the command section.
- **To specify the NAND Flash address that must be read or written**, the software must write the address value to any memory location in the address section. Since an address can be 4 or 5 bytes long (depending on the actual memory size), several consecutive write operations to the address section are required to specify the full address.
- **To read or write data,** the software reads or writes the data from/to any memory location in the data section.

Since the NAND Flash memory automatically increments addresses, there is no need to increment the address of the data section to access consecutive memory locations.

25.6 NOR Flash/PSRAM controller

The FMC generates the appropriate signal timings to drive the following types of memories:

- Asynchronous SRAM, FRAM and ROM
  - 8 bits
  - 16 bits

- PSRAM (CellularRAM™)
  - Asynchronous mode
  - Burst mode for synchronous accesses
  - Multiplexed or non-multiplexed
- NOR Flash memory
  - Asynchronous mode
  - Burst mode for synchronous accesses
  - Multiplexed or non-multiplexed

The FMC outputs a unique chip select signal, NE[4:1], per bank. All the other signals (addresses, data and control) are shared.

The FMC supports a wide range of devices through a programmable timings among which:

- Programmable wait states (up to 15)
- Programmable bus turnaround cycles (up to 15)
- Programmable output enable and write enable delays (up to 15)
- Independent read and write timings and protocol to support the widest variety of memories and timings
- Programmable continuous clock (FMC_CLK) output.

The FMC Clock (FMC_CLK) is a submultiple of the HCLK clock. It can be delivered to the selected external device either during synchronous accesses only or during asynchronous and synchronous accesses depending on the CCKEN bit configuration in the FMC_BCR1 register:

- If the CCLKEN bit is reset, the FMC generates the clock (CLK) only during synchronous accesses (Read/write transactions).
- If the CCLKEN bit is set, the FMC generates a continuous clock during asynchronous and synchronous accesses. To generate the FMC_CLK continuous clock, Bank 1 must be configured in Synchronous mode (see *Section 25.6.6: NOR/PSRAM controller registers*). Since the same clock is used for all synchronous memories, when a continuous output clock is generated and synchronous accesses are performed, the AHB data size has to be the same as the memory data width (MWID) otherwise the FMC_CLK frequency is changed depending on AHB data transaction (refer to *Section 25.6.5: Synchronous transactions* for FMC_CLK divider ratio formula).

The size of each bank is fixed and equal to 64 Mbytes. Each bank is configured through dedicated registers (see *Section 25.6.6: NOR/PSRAM controller registers*).

The programmable memory parameters include access times (see *Table 184*) and support for wait management (for PSRAM and NOR Flash accessed in Burst mode).

Table 184. Programmable NOR/PSRAM access parameters

Parameter	Function	Access mode	Unit	Min.	Max.
Address setup	Duration of the address setup phase	Asynchronous	AHB clock cycle (HCLK)	0	15
Address hold	Duration of the address hold phase	Asynchronous, muxed I/Os	AHB clock cycle (HCLK)	1	15
NBL setup	Duration of the byte lanes setup phase	Asynchronous	AHB clock cycle (HCLK)	0	3

Table 184. Programmable NOR/PSRAM access parameters (continued)

Parameter	Function	Access mode	Unit	Min.	Max.
Data setup	Duration of the data setup phase	Asynchronous	AHB clock cycle (HCLK)	1	256
Data hold	Duration of the data hold phase	Asynchronous	AHB clock cycle (HCLK)	0	3
Bust turn	Duration of the bus turnaround phase	Asynchronous and synchronous read / write	AHB clock cycle (HCLK)	0	15
Clock divide ratio	Number of AHB clock cycles (HCLK) to build one memory clock cycle (CLK)	Synchronous	AHB clock cycle (HCLK)	2	16
Data latency	Number of clock cycles to issue to the memory before the first data of the burst	Synchronous	Memory clock cycle (CLK)	2	17

25.6.1 External memory interface signals

Table 185, *Table 186* and *Table 187* list the signals that are typically used to interface with NOR Flash memory, SRAM and PSRAM.

Note: The prefix "N" identifies the signals that are active low.

NOR Flash memory, non-multiplexed I/Os

Table 185. Non-multiplexed I/O NOR Flash memory

FMC signal name	I/O	Function
CLK	O	Clock (for synchronous access)
A[25:0]	O	Address bus
D[15:0]	I/O	Bidirectional data bus
NE[x]	O	Chip select, x = 1..4
NOE	O	Output enable
NWE	O	Write enable
NL(=NADV)	O	Latch enable (this signal is called address valid, NADV, by some NOR Flash devices)
NWAIT	I	NOR Flash wait input signal to the FMC

The maximum capacity is 512 Mbits (26 address lines).

NOR Flash memory, 16-bit multiplexed I/Os

Table 186. 16-bit multiplexed I/O NOR Flash memory

FMC signal name	I/O	Function
CLK	O	Clock (for synchronous access)
A[25:16]	O	Address bus
AD[15:0]	I/O	16-bit multiplexed, bidirectional address/data bus (the 16-bit address A[15:0] and data D[15:0] are multiplexed on the databus)
NE[x]	O	Chip select, x = 1..4
NOE	O	Output enable
NWE	O	Write enable
NL(=NADV)	O	Latch enable (this signal is called address valid, NADV, by some NOR Flash devices)
NWAIT	I	NOR Flash wait input signal to the FMC

The maximum capacity is 512 Mbits.

PSRAM/FRAM/SRAM, non-multiplexed I/Os

Table 187. Non-multiplexed I/Os PSRAM/SRAM

FMC signal name	I/O	Function
CLK	O	Clock (only for PSRAM synchronous access)
A[25:0]	O	Address bus
D[15:0]	I/O	Data bidirectional bus
NE[x]	O	Chip select, x = 1..4 (called NCE by PSRAM (CellularRAM™ i.e. CRAM))
NOE	O	Output enable
NWE	O	Write enable
NL(= NADV)	O	Address valid only for PSRAM input (memory signal name: NADV)
NWAIT	I	PSRAM wait input signal to the FMC
NBL[1:0]	O	Byte lane output. Byte 0 and Byte 1 control (upper and lower byte enable)

The maximum capacity is 512 Mbits.

PSRAM, 16-bit multiplexed I/Os

Table 188. 16-Bit multiplexed I/O PSRAM

FMC signal name	I/O	Function
CLK	O	Clock (for synchronous access)
A[25:16]	O	Address bus
AD[15:0]	I/O	16-bit multiplexed, bidirectional address/data bus (the 16-bit address A[15:0] and data D[15:0] are multiplexed on the databus)

Table 188. 16-Bit multiplexed I/O PSRAM (continued)

FMC signal name	I/O	Function
NE[x]	O	Chip select, x = 1..4 (called NCE by PSRAM (CellularRAM™ i.e. CRAM))
NOE	O	Output enable
NWE	O	Write enable
NL(= NADV)	O	Address valid PSRAM input (memory signal name: NADV)
NWAIT	I	PSRAM wait input signal to the FMC
NBL[1:0]	O	Byte lane output. Byte 0 and Byte 1 control (upper and lower byte enable)

The maximum capacity is 512 Mbits (26 address lines).

25.6.2 Supported memories and transactions

Table 189 below shows an example of the supported devices, access modes and transactions when the memory data bus is 16-bit wide for NOR Flash memory, PSRAM and SRAM. The transactions not allowed (or not supported) by the FMC are shown in gray in this example.

Table 189. NOR Flash/PSRAM: example of supported memories and transactions

Device	Mode	R/W	AHB data size	Memory data size	Allowed/ not allowed	Comments
NOR Flash (muxed I/Os and nonmuxed I/Os)	Asynchronous	R	8	16	Y	-
	Asynchronous	W	8	16	N	-
	Asynchronous	R	16	16	Y	-
	Asynchronous	W	16	16	Y	-
	Asynchronous	R	32	16	Y	Split into 2 FMC accesses
	Asynchronous	W	32	16	Y	Split into 2 FMC accesses
	Asynchronous page	R	-	16	N	Mode is not supported
	Synchronous	R	8	16	N	-
	Synchronous	R	16	16	Y	-
	Synchronous	R	32	16	Y	-

Table 189. NOR Flash/PSRAM: example of supported memories and transactions (continued)

Device	Mode	R/W	AHB data size	Memory data size	Allowed/ not allowed	Comments
PSRAM (multiplexed I/Os and non-multiplexed I/Os)	Asynchronous	R	8	16	Y	-
	Asynchronous	W	8	16	Y	Use of byte lanes NBL[1:0]
	Asynchronous	R	16	16	Y	-
	Asynchronous	W	16	16	Y	-
	Asynchronous	R	32	16	Y	Split into 2 FMC accesses
	Asynchronous	W	32	16	Y	Split into 2 FMC accesses
	Asynchronous page	R	-	16	N	Mode is not supported
	Synchronous	R	8	16	N	-
	Synchronous	R	16	16	Y	-
	Synchronous	R	32	16	Y	-
	Synchronous	W	8	16	Y	Use of byte lanes NBL[1:0]
	Synchronous	W	16/32	16	Y	-
SRAM and ROM	Asynchronous	R	8 / 16	16	Y	-
	Asynchronous	W	8 / 16	16	Y	Use of byte lanes NBL[1:0]
	Asynchronous	R	32	16	Y	Split into 2 FMC accesses
	Asynchronous	W	32	16	Y	Split into 2 FMC accesses Use of byte lanes NBL[1:0]

25.6.3 General timing rules

Signals synchronization

- All controller output signals change on the rising edge of the internal clock (HCLK)
- In Synchronous mode (read or write), all output signals change on the rising edge of HCLK. Whatever the CLKDIV value, all outputs change as follows:
  - NOEL/NWEL/ NEL/NADVL/ NADVH /NBLL/ Address valid outputs change on the falling edge of FMC_CLK clock.
  - NOEH/ NWEH / NEH/ NOEH/NBLH/ Address invalid outputs change on the rising edge of FMC_CLK clock.

25.6.4 NOR Flash/PSRAM controller asynchronous transactions

Asynchronous static memories (NOR Flash, PSRAM, SRAM, FRAM)

- Signals are synchronized by the internal clock HCLK. This clock is not issued to the memory

- The FMC always samples the data before de-asserting the NOE signal. This guarantees that the memory data hold timing constraint is met (minimum Chip Enable high to data transition is usually 0 ns)
- If the Extended mode is enabled (EXTMOD bit is set in the FMC_BCRx register), up to four extended modes (A, B, C and D) are available. It is possible to mix A, B, C and D modes for read and write operations. For example, read operation can be performed in mode A and write in mode B.
- If the Extended mode is disabled (EXTMOD bit is reset in the FMC_BCRx register), the FMC can operate in mode 1 or mode 2 as follows:
  - Mode 1 is the default mode when SRAM/PSRAM memory type is selected (MTYP = 0x0 or 0x01 in the FMC_BCRx register)
  - Mode 2 is the default mode when NOR memory type is selected (MTYP = 0x10 in the FMC_BCRx register).

Mode 1 - SRAM/FRAM/PSRAM (CRAM)

The next figures show the read and write transactions for the supported modes followed by the required configuration of FMC_BCRx, and FMC_BTRx/FMC_BWTRx registers.

Figure 108. Mode 1 read access waveforms

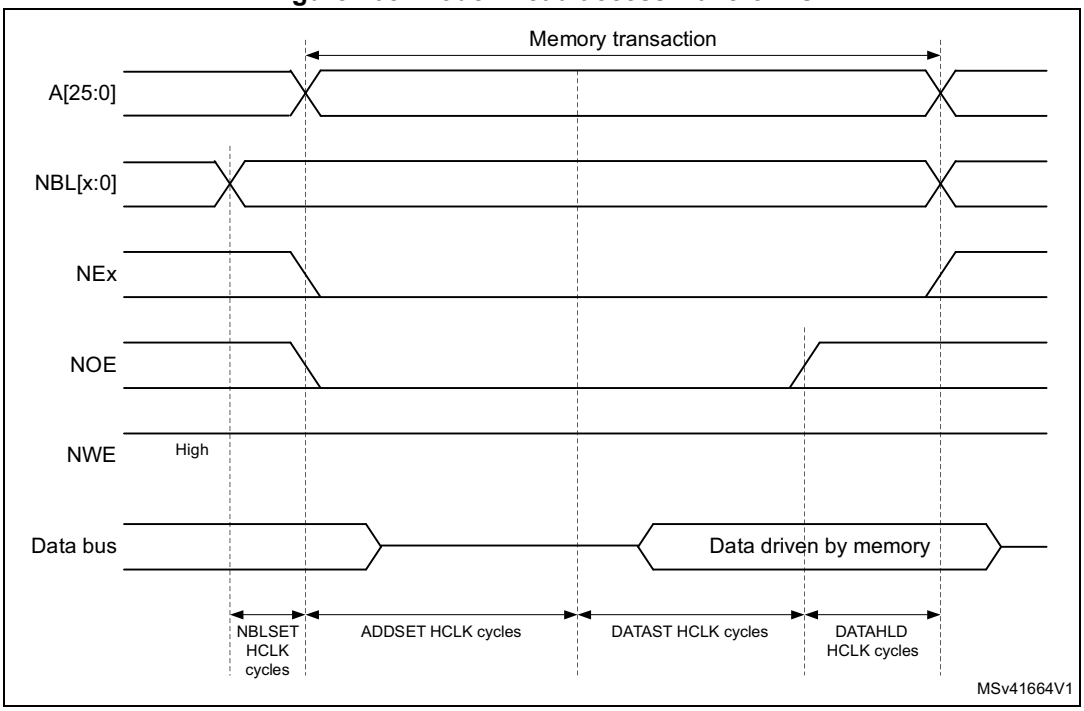
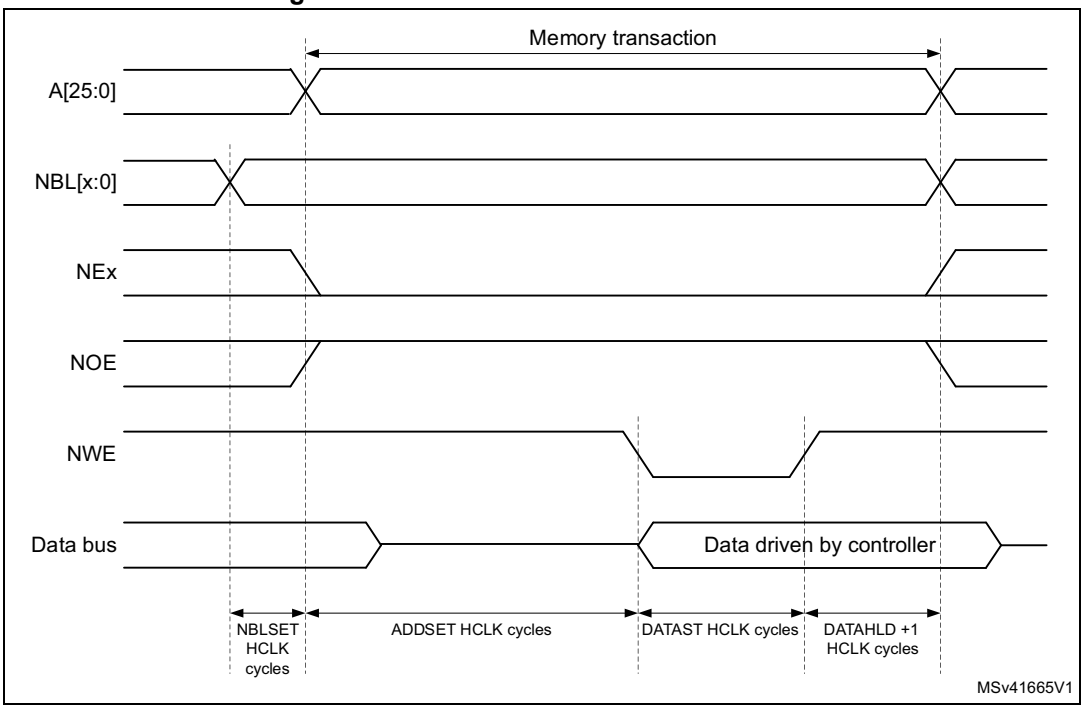


Figure 109. Mode 1 write access waveforms



The DATAHLD time at the end of the read and write transactions guarantee the address and data hold time after the NOE/NWE rising edge. The DATAST value must be greater than zero (DATAST > 0).

Table 190. FMC_BCRx bitfields (mode 1)

Bit number	Bit name	Value to set
31	FMCEN	0x1
30:24	Reserved	0x000
23:22	NBLSET[1:0]	As needed
20	CCLKEN	As needed
19	CBURSTRW	0x0 (no effect in Asynchronous mode)
18:16	CPSIZE	0x0 (no effect in Asynchronous mode)
15	ASYNCWAIT	Set to 1 if the memory supports this feature. Otherwise keep at 0.
14	EXTMOD	0x0
13	WAITEN	0x0 (no effect in Asynchronous mode)
12	WREN	As needed
10	Reserved	0x0
9	WAITPOL	Meaningful only if bit 15 is 1
8	BURSTEN	0x0
7	Reserved	0x1
6	FACCEN	Don’t care

Table 190. FMC_BCRx bitfields (mode 1) (continued)

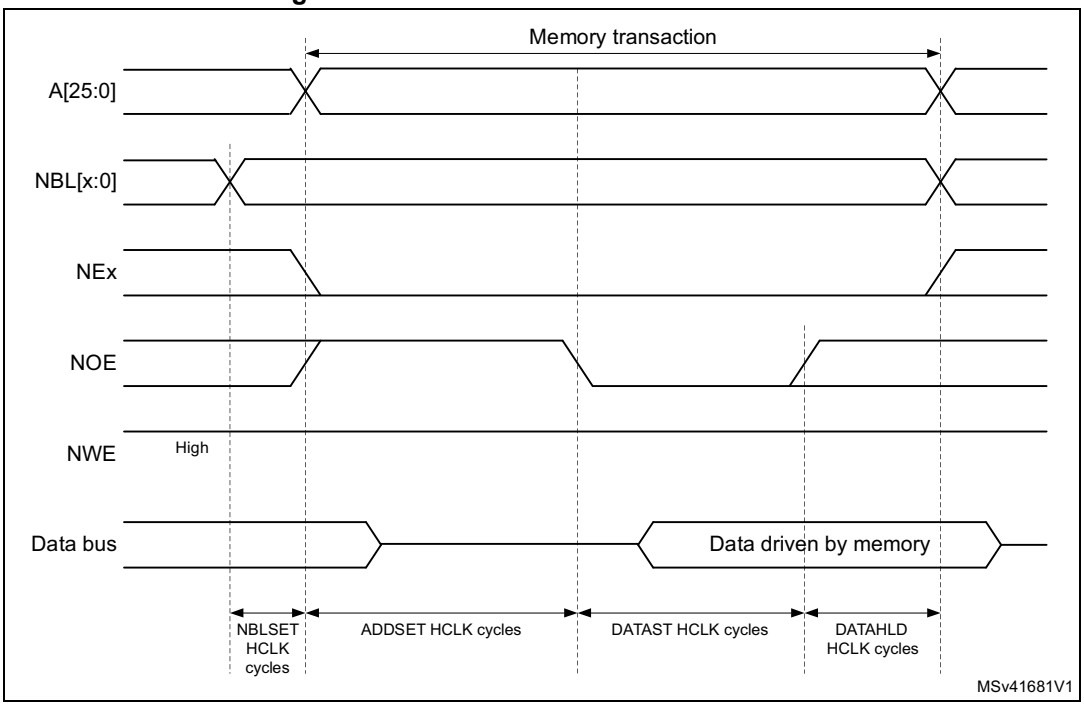
Bit number	Bit name	Value to set
5:4	MWID	As needed
3:2	MTYP	As needed, exclude 0x2 (NOR Flash memory)
1	MUXE	0x0
0	MBKEN	0x1

Table 191. FMC_BTRx bitfields (mode 1)

Bit number	Bit name	Value to set
31:30	DATAHLD	Duration of the data hold phase (DATAHLD HCLK cycles for read accesses, DATAHLD+1 HCLK cycles for write accesses).
29:28	ACCMOD	Don’t care
27:24	DATLAT	Don’t care
23:20	CLKDIV	Don’t care
19:16	BUSTURN	Time between NEx high to NEx low (BUSTURN HCLK).
15:8	DATAST	Duration of the second access phase (DATAST HCLK cycles).
7:4	ADDHLD	Don’t care
3:0	ADDSET	Duration of the first access phase (ADDSET HCLK cycles). Minimum value for ADDSET is 0.

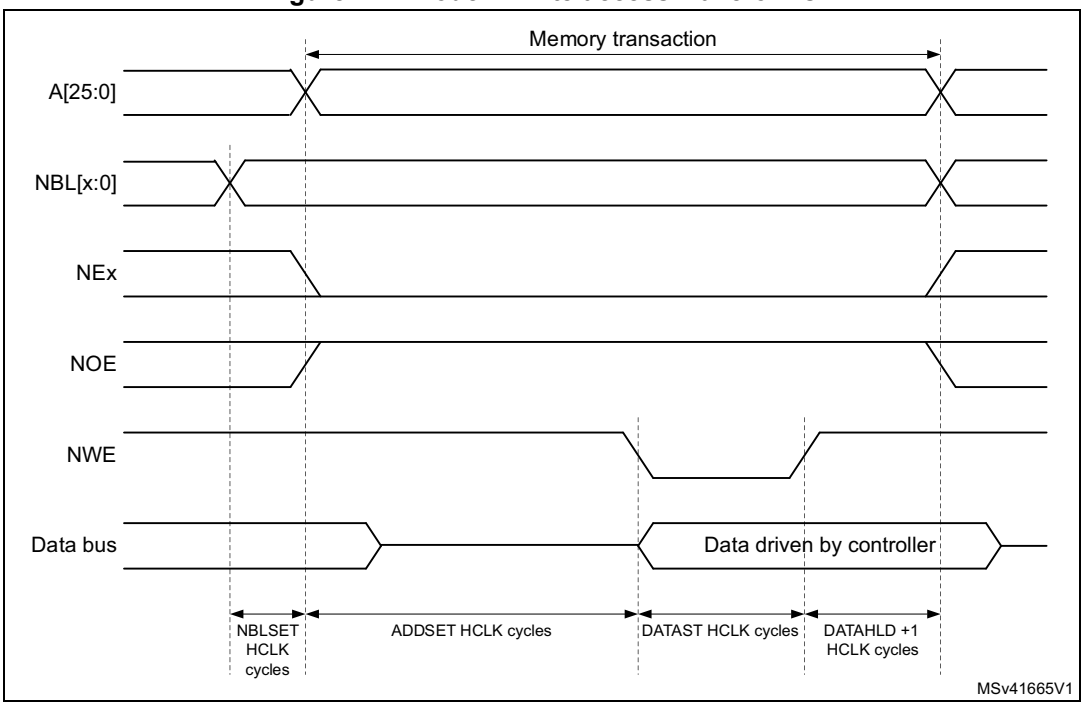
Mode A - SRAM/FRAM/PSRAM (CRAM) OE toggling

Figure 110. Mode A read access waveforms



1. NBL[1:0] are driven low during the read access

Figure 111. Mode A write access waveforms



The differences compared with Mode 1 are the toggling of NOE and the independent read and write timings.

Table 192. FMC_BCRx bitfields (mode A)

Bit number	Bit name	Value to set
31	FMCEN	0x1
30:24	Reserved	0x000
23:22	NBLSET[1:0]	As needed
20	CCLKEN	As needed
19	CBURSTRW	0x0 (no effect in Asynchronous mode)
18:16	CPSIZE	0x0 (no effect in Asynchronous mode)
15	ASYNCWAIT	Set to 1 if the memory supports this feature. Otherwise keep at 0.
14	EXTMOD	0x1
13	WAITEN	0x0 (no effect in Asynchronous mode)
12	WREN	As needed
11	WAITCFG	Don’t care
10	Reserved	0x0
9	WAITPOL	Meaningful only if bit 15 is 1
8	BURSTEN	0x0
7	Reserved	0x1
6	FACCEN	Don’t care
5:4	MWID	As needed
3:2	MTYP	As needed, exclude 0x2 (NOR Flash memory)
1	MUXEN	0x0
0	MBKEN	0x1

Table 193. FMC_BTRx bitfields (mode A)

Bit number	Bit name	Value to set
31:30	DATAHLD	Duration of the data hold phase (DATAHLD HCLK cycles for read accesses).
29:28	ACCMOD	0x0
27:24	DATLAT	Don’t care
23:20	CLKDIV	Don’t care
19:16	BUSTURN	Time between NEx high to NEx low (BUSTURN HCLK).
15:8	DATAST	Duration of the second access phase (DATAST HCLK cycles) for read accesses.
7:4	ADDHLD	Don’t care
3:0	ADDSET	Duration of the first access phase (ADDSET HCLK cycles) for read accesses. Minimum value for ADDSET is 0.

Table 194. FMC_BWTRx bitfields (mode A)

Bit number	Bit name	Value to set
31:30	DATAHLD	Duration of the data hold phase (DATAHLD+1 HCLK cycles for write accesses).
29:28	ACCMOD	0x0
27:24	DATLAT	Don't care
23:20	CLKDIV	Don't care
19:16	BUSTURN	Time between NEx high to NEx low (BUSTURN HCLK).
15:8	DATAST	Duration of the second access phase (DATAST HCLK cycles) for write accesses.
7:4	ADDHLD	Don't care
3:0	ADDSET	Duration of the first access phase (ADDSET HCLK cycles) for write accesses. Minimum value for ADDSET is 0.

Mode 2/B - NOR Flash

Figure 112. Mode 2 and mode B read access waveforms

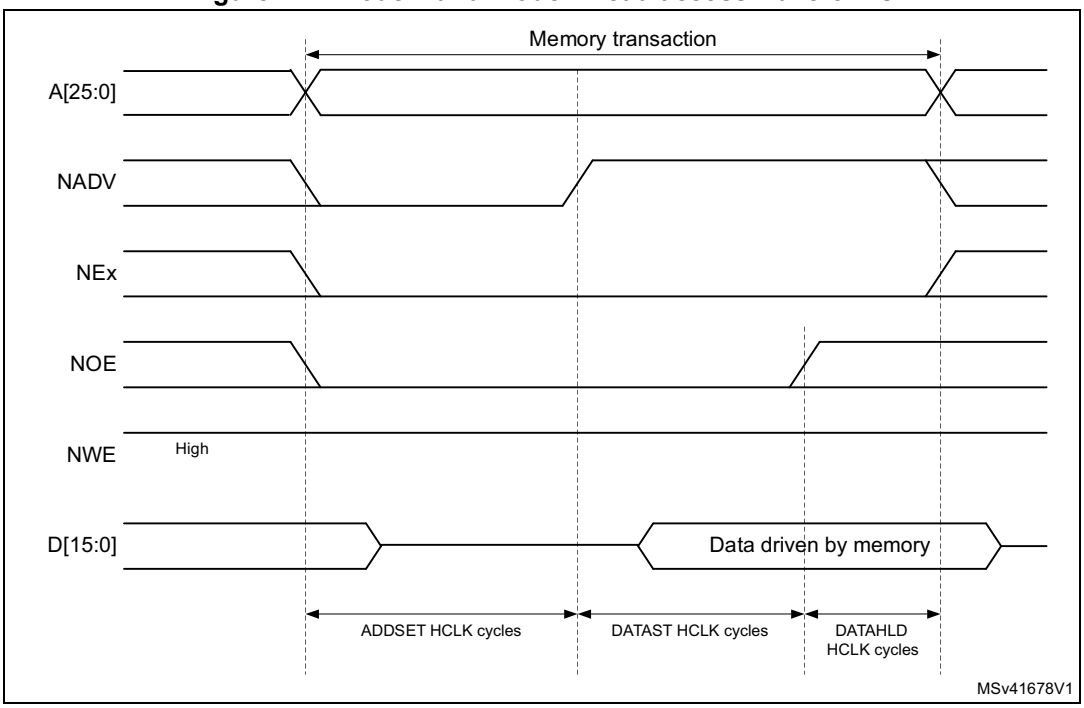


Figure 113. Mode 2 write access waveforms

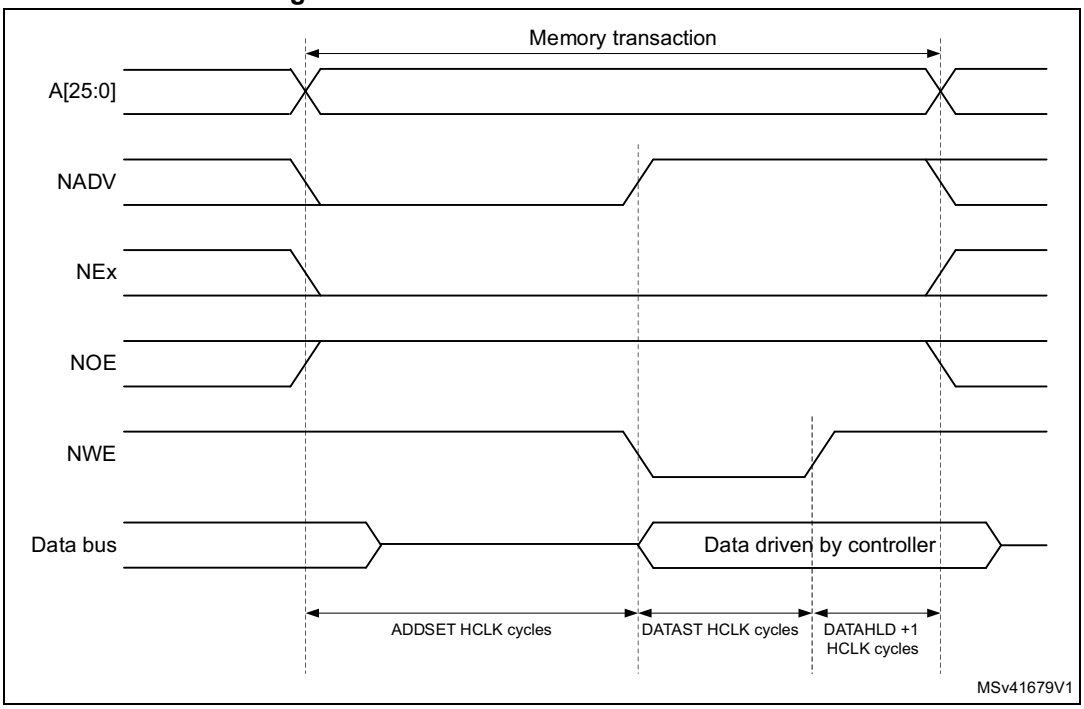
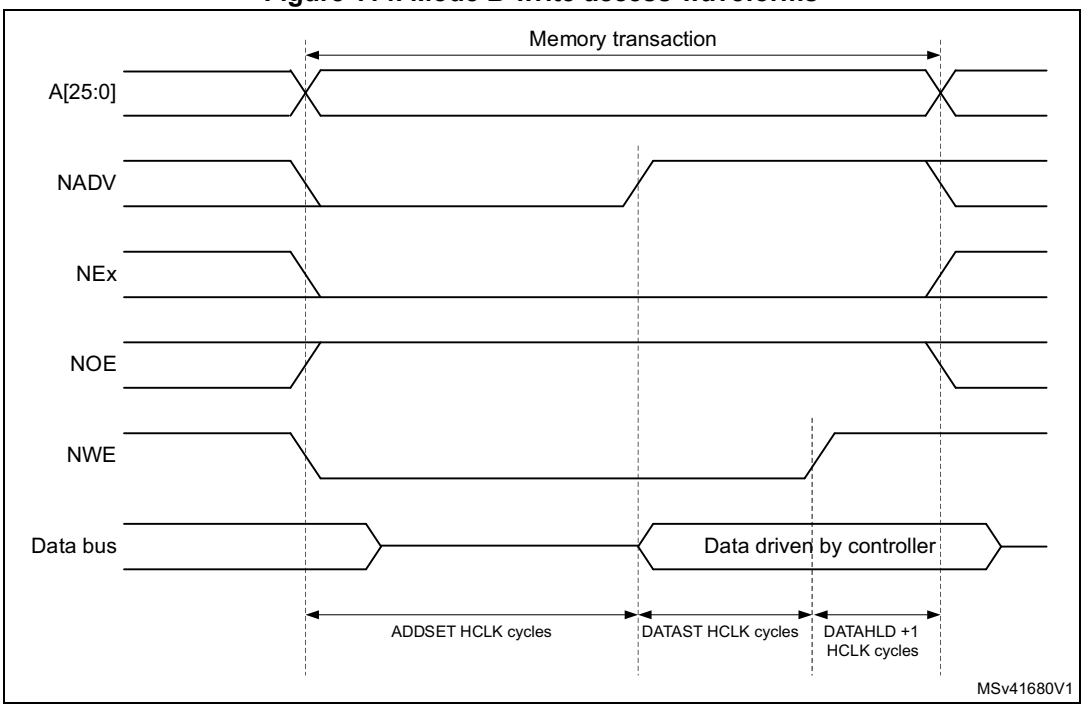


Figure 114. Mode B write access waveforms



The differences with mode 1 are the toggling of NWE and the independent read and write timings when extended mode is set (mode B).

Table 195. FMC_BCRx bitfields (mode 2/B)

Bit number	Bit name	Value to set
31	FMCEN	0x1
30:24	Reserved	0x000
23:22	NBLSET[1:0]	Don’t care
20	CCLKEN	As needed
19	CBURSTRW	0x0 (no effect in Asynchronous mode)
18:16	CPSIZE	0x0 (no effect in Asynchronous mode)
15	ASYNCWAIT	Set to 1 if the memory supports this feature. Otherwise keep at 0.
14	EXTMOD	0x1 for mode B, 0x0 for mode 2
13	WAITEN	0x0 (no effect in Asynchronous mode)
12	WREN	As needed
11	WAITCFG	Don’t care
10	Reserved	0x0
9	WAITPOL	Meaningful only if bit 15 is 1
8	BURSTEN	0x0
7	Reserved	0x1
6	FACCEN	0x1
5:4	MWID	As needed
3:2	MTYP	0x2 (NOR Flash memory)
1	MUXEN	0x0
0	MBKEN	0x1

Table 196. FMC_BTRx bitfields (mode 2/B)

Bit number	Bit name	Value to set
31:30	DATAHLD	Duration of the data hold phase (DATAHLD HCLK cycles for read accesses and DATAHLD+1 HCLK cycles for write accesses when Extended mode is disabled).
29:28	ACCMOD	0x1 if Extended mode is set
27:24	DATLAT	Don’t care
23:20	CLKDIV	Don’t care
19:16	BUSTURN	Time between NEx high to NEx low (BUSTURN HCLK).
15:8	DATAST	Duration of the access second phase (DATAST HCLK cycles) for read accesses.
7:4	ADDHLD	Don’t care
3:0	ADDSET	Duration of the access first phase (ADDSET HCLK cycles) for read accesses. Minimum value for ADDSET is 0.

Table 197. FMC_BWTRx bitfields (mode 2/B)

Bit number	Bit name	Value to set
31:30	DATAHLD	Duration of the data hold phase (DATAHLD+1 HCLK cycles for write accesses).
29:28	ACCMOD	0x1 if Extended mode is set
27:24	DATLAT	Don't care
23:20	CLKDIV	Don't care
19:16	BUSTURN	Time between NEx high to NEx low (BUSTURN HCLK).
15:8	DATAST	Duration of the access second phase (DATAST HCLK cycles) for write accesses.
7:4	ADDHLD	Don't care
3:0	ADDSET	Duration of the access first phase (ADDSET HCLK cycles) for write accesses. Minimum value for ADDSET is 0.

Note: The FMC_BWTRx register is valid only if the Extended mode is set (mode B), otherwise its content is don't care.

Mode C - NOR Flash - OE toggling

Figure 115. Mode C read access waveforms

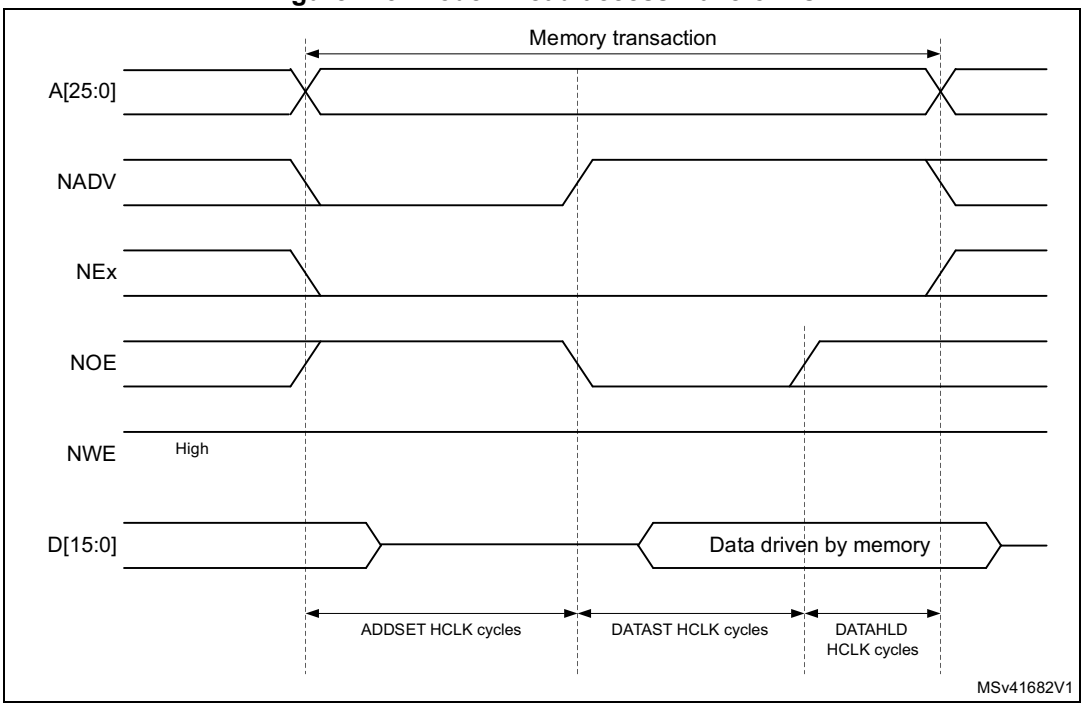
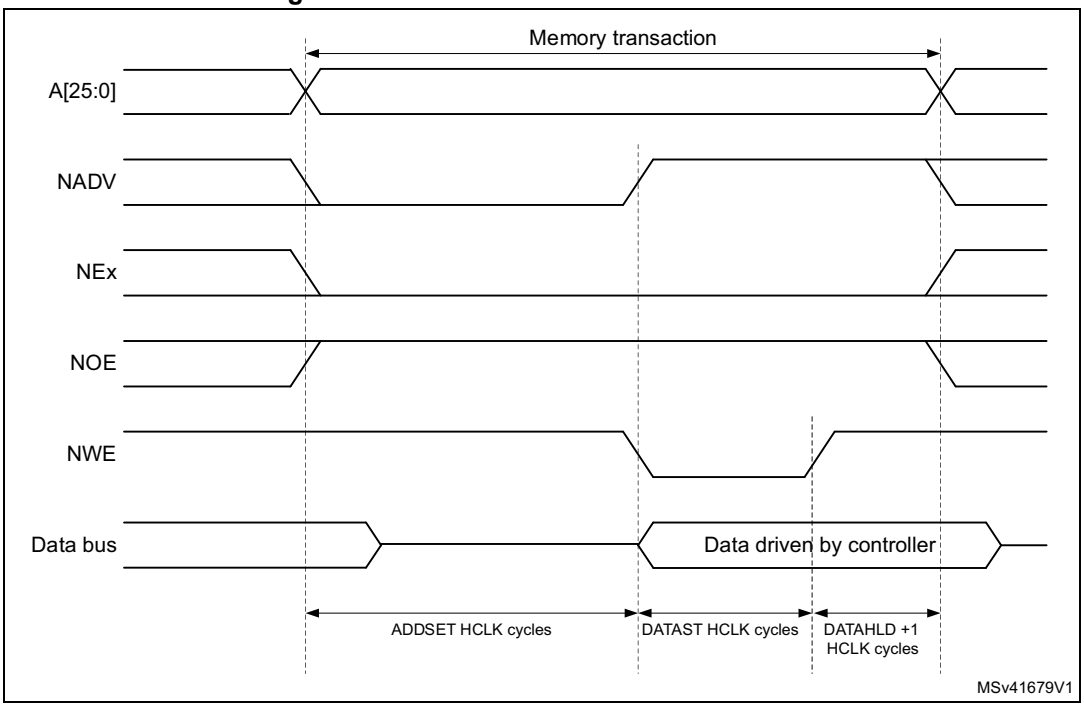


Figure 116. Mode C write access waveforms



The differences compared with mode 1 are the toggling of NOE and the independent read and write timings.

Table 198. FMC_BCRx bitfields (mode C)

Bit number	Bit name	Value to set
31	FMCEN	0x1
30:24	Reserved	0x000
23:22	NBLSET[1:0]	Don’t care
20	CCLKEN	As needed
19	CBURSTRW	0x0 (no effect in Asynchronous mode)
18:16	CPSIZE	0x0 (no effect in Asynchronous mode)
15	ASYNCWAIT	Set to 1 if the memory supports this feature. Otherwise keep at 0.
14	EXTMOD	0x1
13	WAITEN	0x0 (no effect in Asynchronous mode)
12	WREN	As needed
11	WAITCFG	Don’t care
10	Reserved	0x0
9	WAITPOL	Meaningful only if bit 15 is 1
8	BURSTEN	0x0
7	Reserved	0x1
6	FACCEN	0x1

Table 198. FMC_BCRx bitfields (mode C) (continued)

Bit number	Bit name	Value to set
5:4	MWID	As needed
3:2	MTYP	0x02 (NOR Flash memory)
1	MUXEN	0x0
0	MBKEN	0x1

Table 199. FMC_BTRx bitfields (mode C)

Bit number	Bit name	Value to set
31:30	DATAHLD	Duration of the data hold phase (DATAHLD HCLK cycles for read accesses).
29:28	ACCMOD	0x2
27:24	DATLAT	0x0
23:20	CLKDIV	0x0
19:16	BUSTURN	Time between NEx high to NEx low (BUSTURN HCLK).
15:8	DATAST	Duration of the second access phase (DATAST HCLK cycles) for read accesses.
7:4	ADDHLD	Don’t care
3:0	ADDSET	Duration of the first access phase (ADDSET HCLK cycles) for read accesses. Minimum value for ADDSET is 0.

Table 200. FMC_BWTRx bitfields (mode C)

Bit number	Bit name	Value to set
31:30	DATAHLD	Duration of the data hold phase (DATAHLD+1 HCLK cycles for write accesses).
29:28	ACCMOD	0x2
27:24	DATLAT	Don’t care
23:20	CLKDIV	Don’t care
19:16	BUSTURN	Time between NEx high to NEx low (BUSTURN HCLK).
15:8	DATAST	Duration of the second access phase (DATAST HCLK cycles) for write accesses.
7:4	ADDHLD	Don’t care
3:0	ADDSET	Duration of the first access phase (ADDSET HCLK cycles) for write accesses. Minimum value for ADDSET is 0.

Mode D - asynchronous access with extended address

Figure 117. Mode D read access waveforms

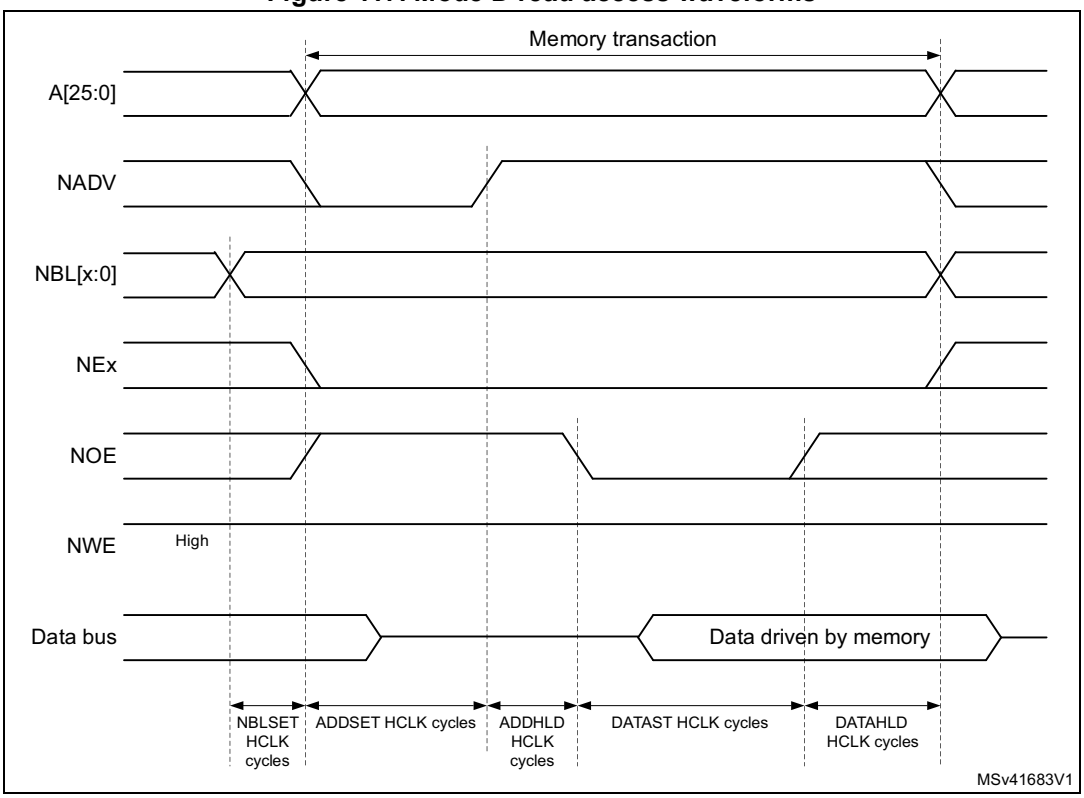
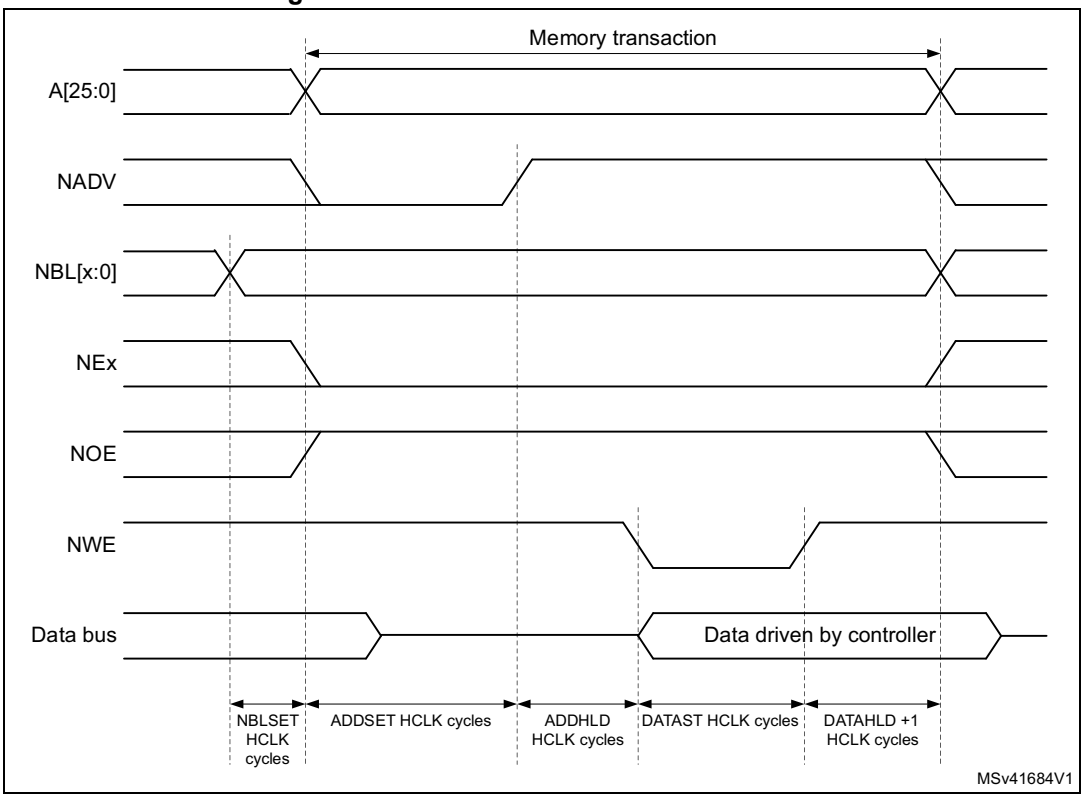


Figure 118. Mode D write access waveforms



The differences with mode 1 are the toggling of NOE that goes on toggling after NADV changes and the independent read and write timings.

Table 201. FMC_BCRx bitfields (mode D)

Bit number	Bit name	Value to set
31	FMCEN	0x1
30:24	Reserved	0x000
23:22	NBLSET[1:0]	As needed
20	CCLKEN	As needed
19	CBURSTRW	0x0 (no effect in Asynchronous mode)
18:16	CPSIZE	0x0 (no effect in Asynchronous mode)
15	ASYNCWAIT	Set to 1 if the memory supports this feature. Otherwise keep at 0.
14	EXTMOD	0x1
13	WAITEN	0x0 (no effect in Asynchronous mode)
12	WREN	As needed
11	WAITCFG	Don’t care
10	Reserved	0x0
9	WAITPOL	Meaningful only if bit 15 is 1
8	BURSTEN	0x0

Table 201. FMC_BCRx bitfields (mode D) (continued)

Bit number	Bit name	Value to set
7	Reserved	0x1
6	FACCEN	Set according to memory support
5:4	MWID	As needed
3:2	MTYP	As needed
1	MUXEN	0x0
0	MBKEN	0x1

Table 202. FMC_BTRx bitfields (mode D)

Bit number	Bit name	Value to set
31:30	DATAHLD	Duration of the data hold phase (DATAHLD HCLK cycles for read accesses).
29:28	ACCMOD	0x3
27:24	DATLAT	Don’t care
23:20	CLKDIV	Don’t care
19:16	BUSTURN	Time between NEx high to NEx low (BUSTURN HCLK).
15:8	DATAST	Duration of the second access phase (DATAST HCLK cycles) for read accesses.
7:4	ADDHLD	Duration of the middle phase of the read access (ADDHLD HCLK cycles)
3:0	ADDSET	Duration of the first access phase (ADDSET HCLK cycles) for read accesses. Minimum value for ADDSET is 1.

Table 203. FMC_BWTRx bitfields (mode D)

Bit number	Bit name	Value to set
31:30	DATAHLD	Duration of the data hold phase (DATAHLD+1 HCLK cycles for write accesses).
29:28	ACCMOD	0x3
27:24	DATLAT	Don’t care
23:20	CLKDIV	Don’t care
19:16	BUSTURN	Time between NEx high to NEx low (BUSTURN HCLK).
15:8	DATAST	Duration of the second access phase (DATAST HCLK cycles).
7:4	ADDHLD	Duration of the middle phase of the write access (ADDHLD HCLK cycles)
3:0	ADDSET	Duration of the first access phase (ADDSET HCLK cycles) for write accesses. Minimum value for ADDSET is 1.

Muxed mode - multiplexed asynchronous access to NOR Flash memory

Figure 119. Muxed read access waveforms

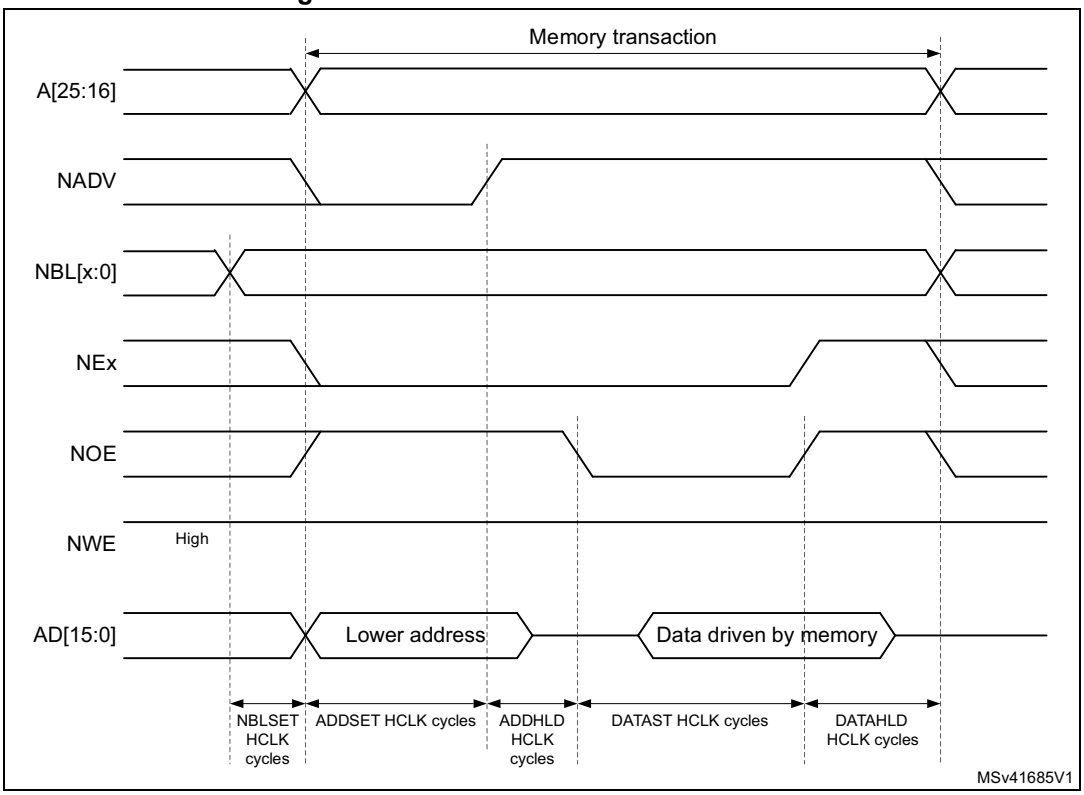
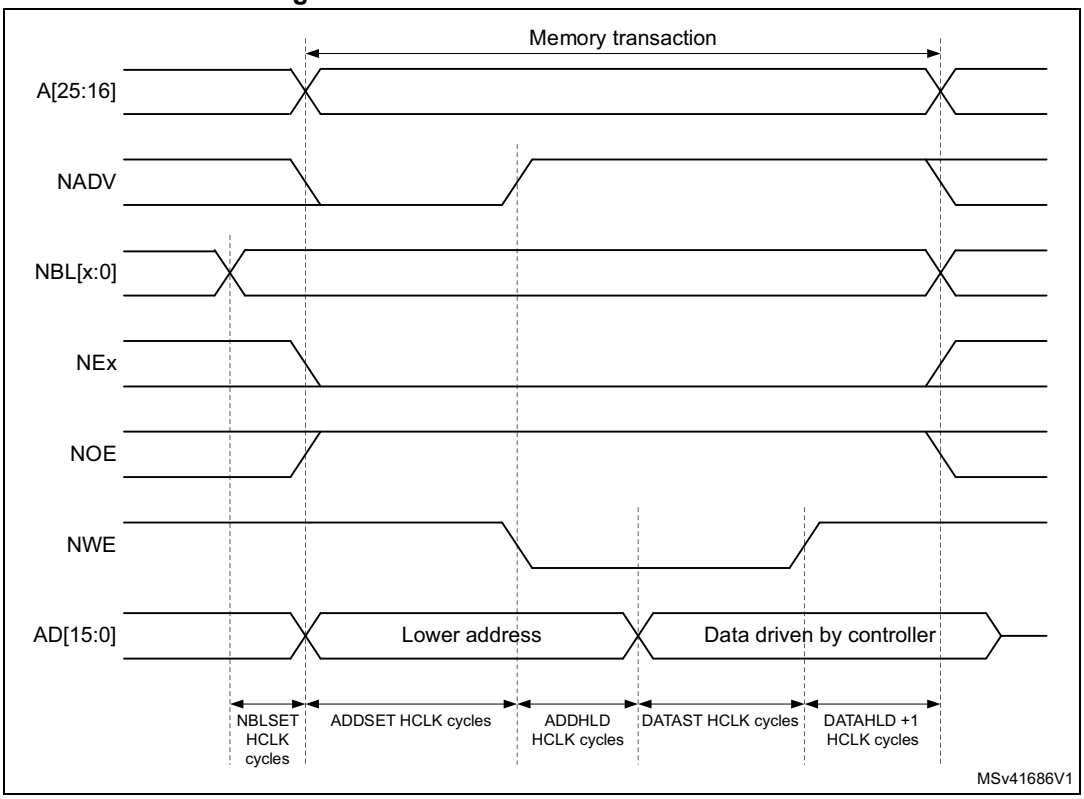


Figure 120. Muxed write access waveforms



The difference with mode D is the drive of the lower address byte(s) on the data bus.

Table 204. FMC_BCRx bitfields (Muxed mode)

Bit number	Bit name	Value to set
31	FMCEN	0x1
30:24	Reserved	0x000
23:22	NBLSET[1:0]	As needed
20	CCLKEN	As needed
19	CBURSTRW	0x0 (no effect in Asynchronous mode)
18:16	CPSIZE	0x0 (no effect in Asynchronous mode)
15	ASYNCWAIT	Set to 1 if the memory supports this feature. Otherwise keep at 0.
14	EXTMOD	0x0
13	WAITEN	0x0 (no effect in Asynchronous mode)
12	WREN	As needed
11	WAITCFG	Don’t care
10	Reserved	0x0
9	WAITPOL	Meaningful only if bit 15 is 1
8	BURSTEN	0x0
7	Reserved	0x1

Table 204. FMC_BCRx bitfields (Muxed mode) (continued)

Bit number	Bit name	Value to set
6	FACCEN	0x1
5:4	MWID	As needed
3:2	MTYP	0x2 (NOR Flash memory) or 0x1(PSRAM)
1	MUXEN	0x1
0	MBKEN	0x1

Table 205. FMC_BTRx bitfields (Muxed mode)

Bit number	Bit name	Value to set
31:30	DATAHLD	Duration of the data hold phase (DATAHLD HCLK cycles for read accesses, DATAHLD+1 HCLK cycles for write accesses).
29:28	ACCMOD	0x0
27:24	DATLAT	Don’t care
23:20	CLKDIV	Don’t care
19:16	BUSTURN	Time between NEx high to NEx low (BUSTURN HCLK).
15:8	DATAST	Duration of the second access phase (DATAST HCLK cycles).
7:4	ADDHLD	Duration of the middle phase of the access (ADDHLD HCLK cycles).
3:0	ADDSET	Duration of the first access phase (ADDSET HCLK cycles). Minimum value for ADDSET is 1.

WAIT management in asynchronous accesses

If the asynchronous memory asserts the WAIT signal to indicate that it is not yet ready to accept or to provide data, the ASYNCWAIT bit has to be set in FMC_BCRx register.

If the WAIT signal is active (high or low depending on the WAITPOL bit), the second access phase (Data setup phase), programmed by the DATAST bits, is extended until WAIT becomes inactive. Unlike the data setup phase, the first access phases (Address setup and Address hold phases), programmed by the ADDSET and ADDHLD bits, are not WAIT sensitive and so they are not prolonged.

The data setup phase must be programmed so that WAIT can be detected 4 HCLK cycles before the end of the memory transaction. The following cases must be considered:

1. The memory asserts the WAIT signal aligned to NOE/NWE which toggles:

$$DATAST \geq (4 \times HCLK) + max\_wait\_assertion\_time$$

2. The memory asserts the WAIT signal aligned to NEx (or NOE/NWE not toggling):
   if

$$max\_wait\_assertion\_time > address\_phase + hold\_phase$$

   then:

$$DATAST \geq (4 \times HCLK) + (max\_wait\_assertion\_time - address\_phase - hold\_phase)$$

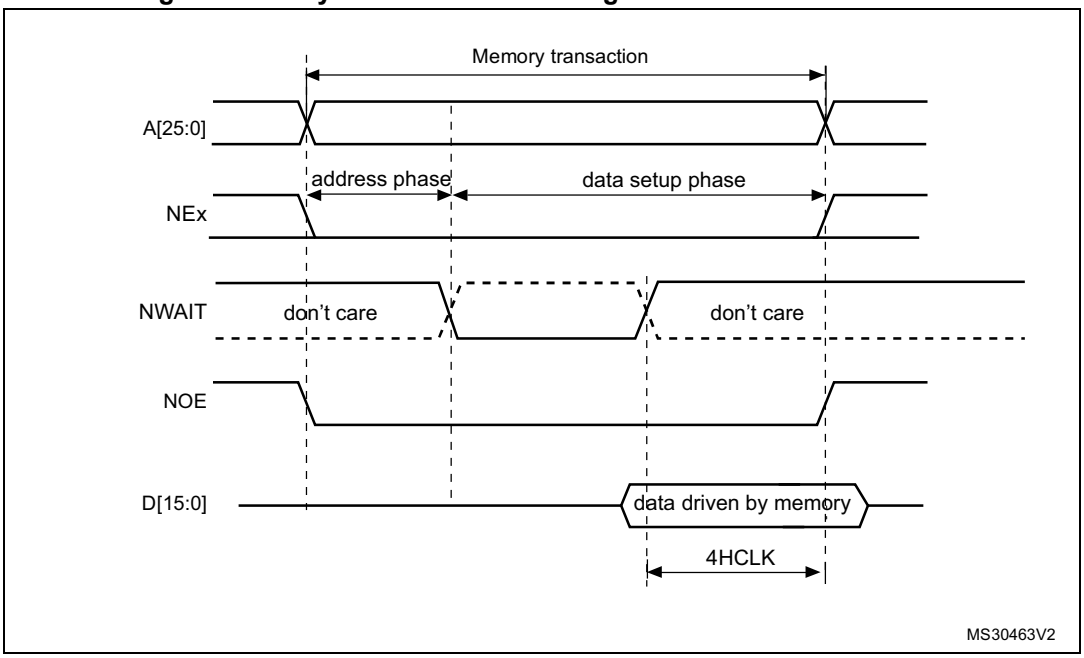
   otherwise

$$DATAST \geq 4 \times HCLK$$

   where max_wait_assertion_time is the maximum time taken by the memory to assert the WAIT signal once NEx/NOE/NWE is low.

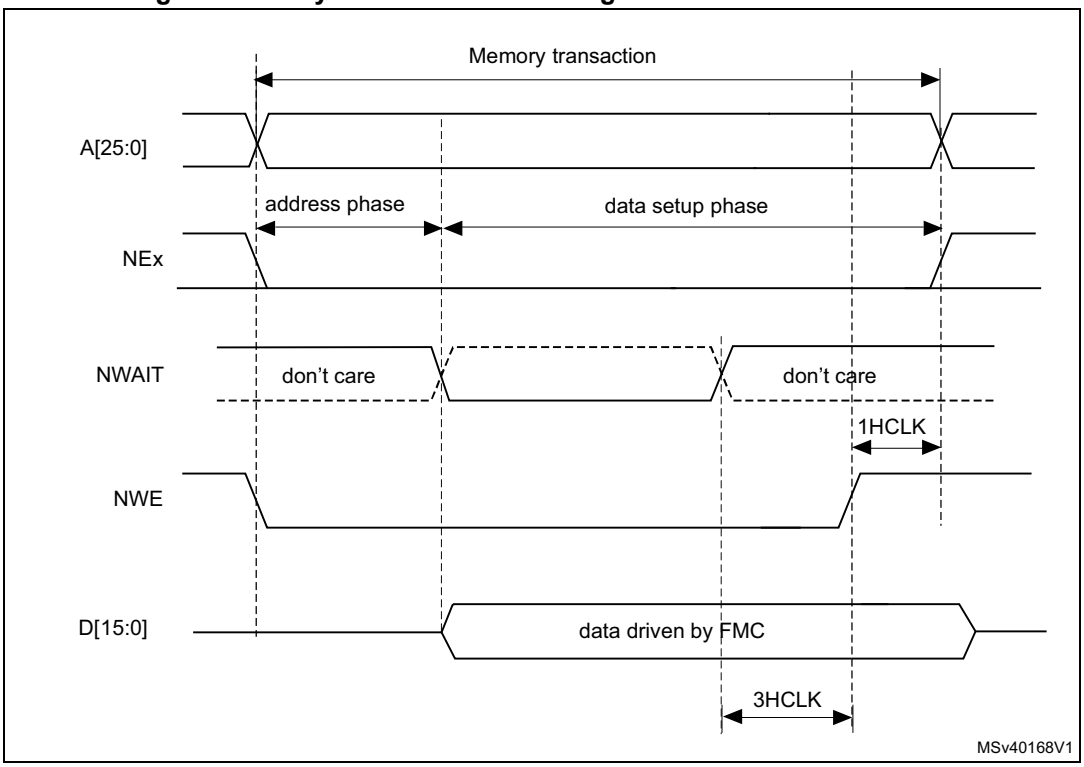
Figure 121 and *Figure 122* show the number of HCLK clock cycles that are added to the memory access phase after WAIT is released by the asynchronous memory (independently of the above cases).

Figure 121. Asynchronous wait during a read access waveforms



1. NWAIT polarity depends on WAITPOL bit setting in FMC_BCRx register.

Figure 122. Asynchronous wait during a write access waveforms



1. NWAIT polarity depends on WAITPOL bit setting in FMC_BCRx register.

CellularRAM™ (PSRAM) refresh management

The CellularRAM™ does not allow maintaining the chip select signal (NE) low for longer than the t_{CEM} timing specified for the memory device. This timing can be programmed in the FMC_PCSCNTR register. It defines the maximum duration of the NE low pulse in HCLK cycles for asynchronous accesses and FMC_CLK cycles for synchronous accesses

25.6.5 Synchronous transactions

The memory clock, FMC_CLK, is a submultiple of HCLK. It depends on the value of CLKDIV and the MWID/ AHB data size, following the formula given below:

Whatever MWID size: 16 or 8-bit, the FMC_CLK divider ratio is always defined by the programmed CLKDIV value.

Example:

- If CLKDIV=1, MWID = 16 bits, AHB data size=8 bits, FMC_CLK=HCLK/2.

NOR Flash memories specify a minimum time from NADV assertion to CLK high. To meet this constraint, the FMC does not issue the clock to the memory during the first internal clock cycle of the synchronous access (before NADV assertion). This guarantees that the rising edge of the memory clock occurs in the middle of the NADV low pulse.

Data latency versus NOR memory latency

The data latency is the number of cycles to wait before sampling the data. The DATLAT value must be consistent with the latency value specified in the NOR Flash configuration

register. The FMC does not include the clock cycle when NADV is low in the data latency count.

Caution: Some NOR Flash memories include the NADV Low cycle in the data latency count, so that the exact relation between the NOR Flash latency and the FMC DATLAT parameter can be either:

- NOR Flash latency = (DATLAT + 2) CLK clock cycles
- or NOR Flash latency = (DATLAT + 3) CLK clock cycles

Some recent memories assert NWAIT during the latency phase. In such cases DATLAT can be set to its minimum value. As a result, the FMC samples the data and waits long enough to evaluate if the data are valid. Thus the FMC detects when the memory exits latency and real data are processed.

Other memories do not assert NWAIT during latency. In this case the latency must be set correctly for both the FMC and the memory, otherwise invalid data are mistaken for good data, or valid data are lost in the initial phase of the memory access.

Single-burst transfer

When the selected bank is configured in Burst mode for synchronous accesses, if for example an AHB single-burst transaction is requested on 16-bit memories, the FMC performs a burst transaction of length 1 (if the AHB transfer is 16 bits), or length 2 (if the AHB transfer is 32 bits) and de-assert the chip select signal when the last data is strobed.

Such transfers are not the most efficient in terms of cycles compared to asynchronous read operations. Nevertheless, a random asynchronous access would first require to re-program the memory access mode, which would altogether last longer.

Cross boundary page for CellularRAM™ 1.5

CellularRAM™ 1.5 does not allow burst access to cross the page boundary. The FMC controller allows to split automatically the burst access when the memory page size is reached by configuring the CPSIZE bits in the FMC_BCR1 register following the memory page size.

Wait management

For synchronous NOR Flash memories, NWAIT is evaluated after the programmed latency period, which corresponds to (DATLAT+2) CLK clock cycles.

If NWAIT is active (low level when WAITPOL = 0, high level when WAITPOL = 1), wait states are inserted until NWAIT is inactive (high level when WAITPOL = 0, low level when WAITPOL = 1).

When NWAIT is inactive, the data is considered valid either immediately (bit WAITCFG = 1) or on the next clock edge (bit WAITCFG = 0).

During wait-state insertion via the NWAIT signal, the controller continues to send clock pulses to the memory, keeping the chip select and output enable signals valid. It does not consider the data as valid.

In Burst mode, there are two timing configurations for the NOR Flash NWAIT signal:

- The Flash memory asserts the NWAIT signal one data cycle before the wait state (default after reset).
- The Flash memory asserts the NWAIT signal during the wait state

The FMC supports both NOR Flash wait state configurations, for each chip select, thanks to the WAITCFG bit in the FMC_BCRx registers (x = 0..3).

Figure 123. Wait configuration waveforms

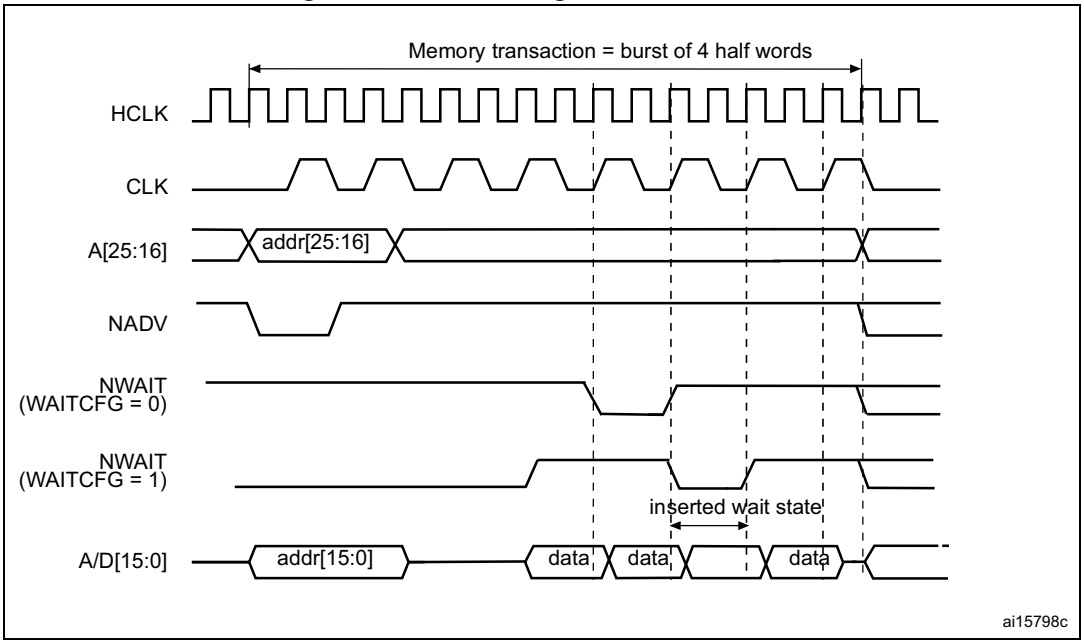
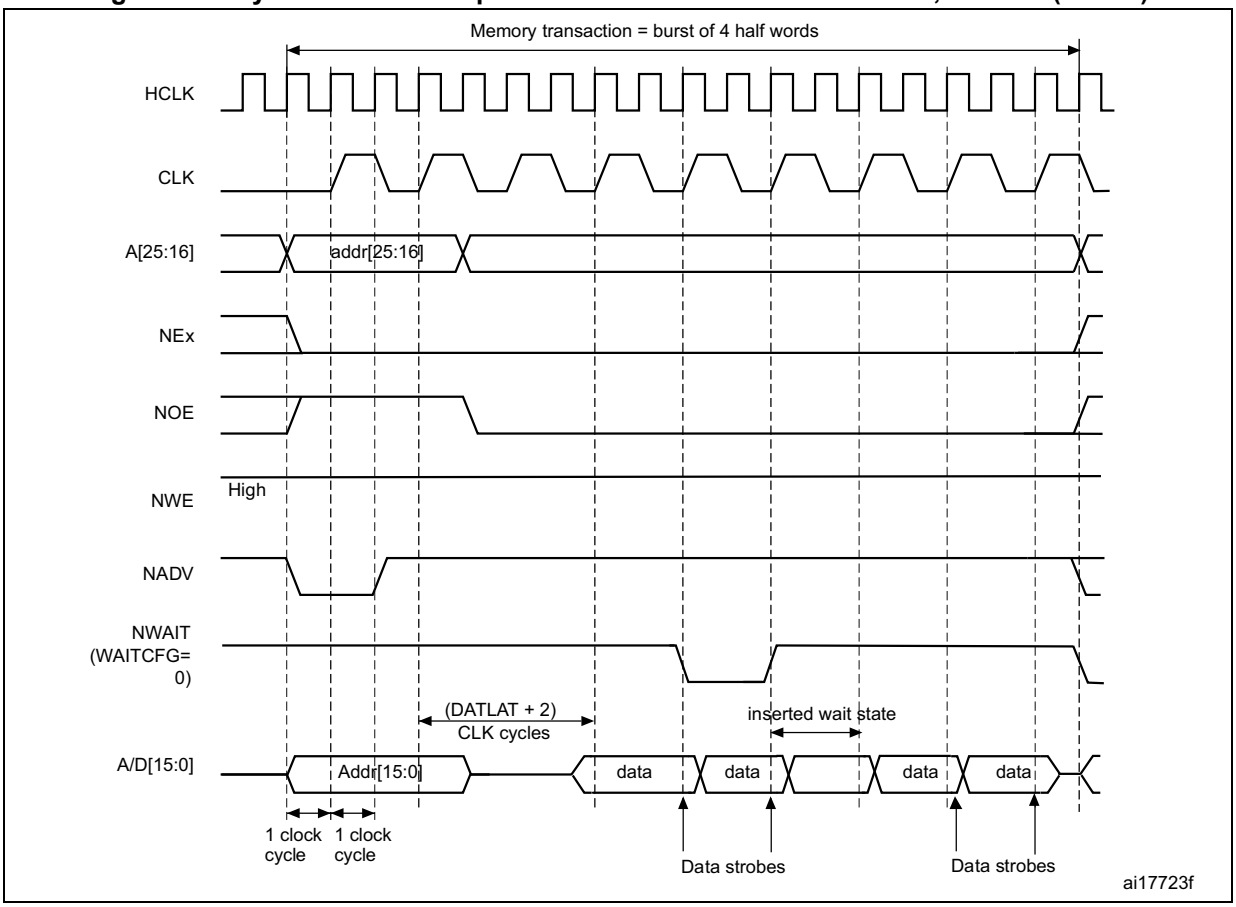


Figure 124. Synchronous multiplexed read mode waveforms - NOR, PSRAM (CRAM)



1. Byte lane outputs (NBL are not shown; for NOR access, they are held high, and, for PSRAM (CRAM) access, they are held low.

Table 206. FMC_BCRx bitfields (Synchronous multiplexed read mode)

Bit number	Bit name	Value to set
31	FMCEN	0x1
30:24	Reserved	0x000
23:22	NBLSET[1:0]	Don’t care
20	CCLKEN	As needed
19	CBURSTRW	No effect on synchronous read
18:16	CPSIZE	0x0 (no effect in Asynchronous mode)
15	ASYNCWAIT	0x0
14	EXTMOD	0x0
13	WAITEN	To be set to 1 if the memory supports this feature, to be kept at 0 otherwise
12	WREN	No effect on synchronous read
11	WAITCFG	To be set according to memory
10	Reserved	0x0

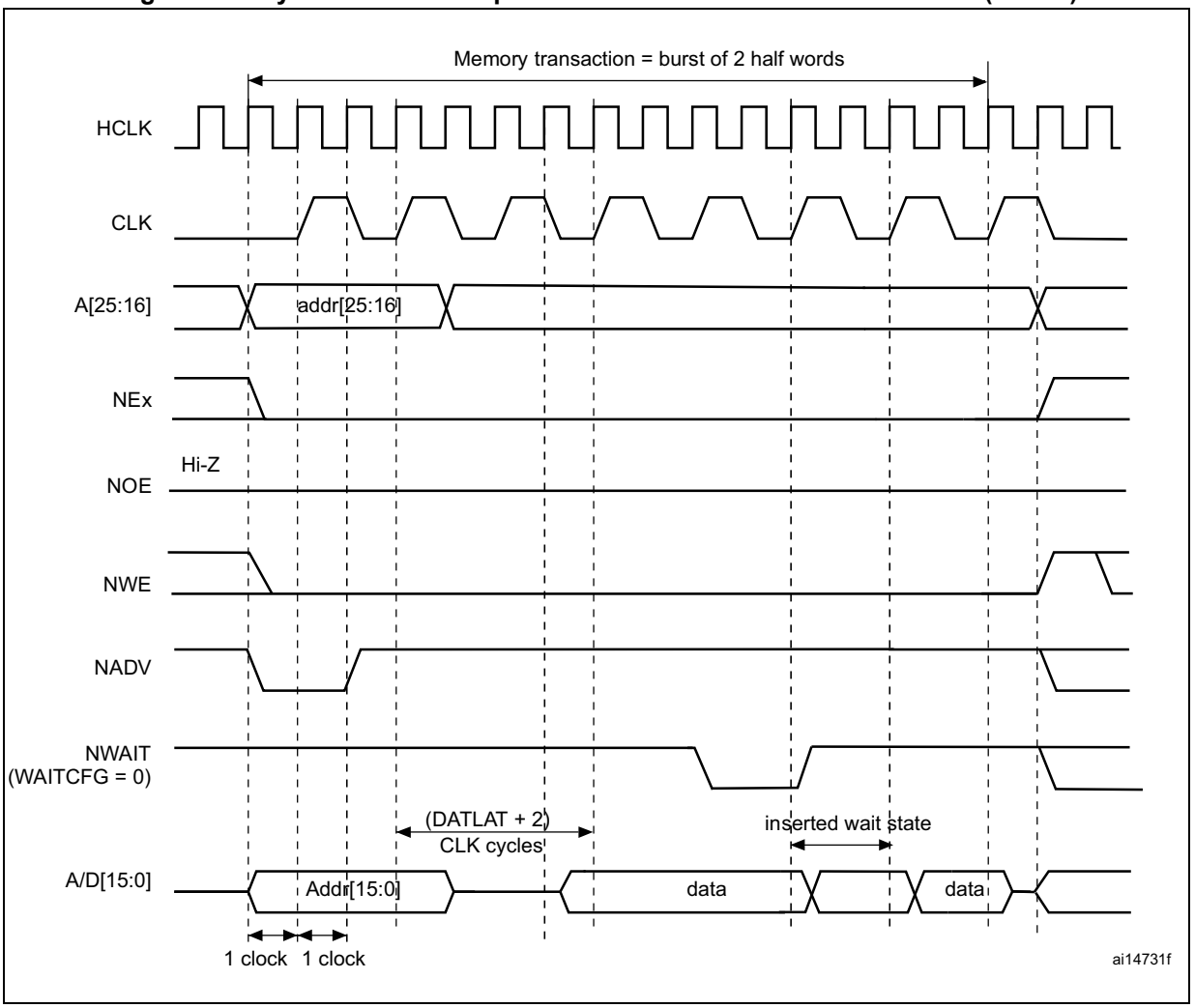
Table 206. FMC_BCRx bitfields (Synchronous multiplexed read mode) (continued)

Bit number	Bit name	Value to set
9	WAITPOL	To be set according to memory
8	BURSTEN	0x1
7	Reserved	0x1
6	FACCEN	Set according to memory support (NOR Flash memory)
5-4	MWID	As needed
3-2	MTYP	0x1 or 0x2
1	MUXEN	As needed
0	MBKEN	0x1

Table 207. FMC_BTRx bitfields (Synchronous multiplexed read mode)

Bit number	Bit name	Value to set
31:30	DATAHLD	Don’t care
29:28	ACCMOD	0x0
27-24	DATLAT	Data latency
27-24	DATLAT	Data latency
23-20	CLKDIV	0x0 to get CLK = HCLK 0x1 to get CLK = 2 × HCLK ..
19-16	BUSTURN	Time between NEx high to NEx low (BUSTURN HCLK).
15-8	DATAST	Don’t care
7-4	ADDHLD	Don’t care
3-0	ADDSET	Don’t care

Figure 125. Synchronous multiplexed write mode waveforms - PSRAM (CRAM)



1. The memory must issue NWAIT signal one cycle in advance, accordingly WAITCFG must be programmed to 0.
2. Byte Lane (NBL) outputs are not shown, they are held low while NEx is active.

Table 208. FMC_BCRx bitfields (Synchronous multiplexed write mode)

Bit number	Bit name	Value to set
31	FMCEN	0x1
30:24	Reserved	0x000
23:22	NBLSET[1:0]	Don’t care
20	CCLKEN	As needed
19	CBURSTRW	0x1
18:16	CPSIZE	As needed (0x1 for CRAM 1.5)
15	ASYNCWAIT	0x0
14	EXTMOD	0x0

Table 208. FMC_BCRx bitfields (Synchronous multiplexed write mode) (continued)

Bit number	Bit name	Value to set
13	WAITEN	To be set to 1 if the memory supports this feature, to be kept at 0 otherwise.
12	WREN	0x1
11	WAITCFG	0x0
10	Reserved	0x0
9	WAITPOL	to be set according to memory
8	BURSTEN	no effect on synchronous write
7	Reserved	0x1
6	FACCEN	Set according to memory support
5-4	MWID	As needed
3-2	MTYP	0x1
1	MUXEN	As needed
0	MBKEN	0x1

Table 209. FMC_BTRx bitfields (Synchronous multiplexed write mode)

Bit number	Bit name	Value to set
31-30	DATAHLD	Don’t care
29:28	ACCMOD	0x0
27-24	DATLAT	Data latency
23-20	CLKDIV	0x0 to get CLK = HCLK 0x1 to get CLK = 2 × HCLK
19-16	BUSTURN	Time between NEx high to NEx low (BUSTURN HCLK).
15-8	DATAST	Don’t care
7-4	ADDHLD	Don’t care
3-0	ADDSET	Don’t care

25.6.6 NOR/PSRAM controller registers

SRAM/NOR-Flash chip-select control register for bank x (FMC_BCRx) (x = 1 to 4)

Address offset: 8 * (x – 1), (x = 1 to 4)

Reset value: Bank 1: 0x0000 30DB

Reset value: Bank 2: 0x0000 30D2

Reset value: Bank 3: 0x0000 30D2

Reset value: Bank 4: 0x0000 30D2

This register contains the control information of each memory bank, used for SRAMs, PSRAM, FRAM and NOR Flash memories.

31	30	29	28	27	26	25	24	23	22	21	20	19	18	17	16
FMCEN	Res.	Res.	Res.	Res.	Res.	Res.	Res.	NBLSET[1:0]		WFDIS	CCLK EN	CBURST RW	CPSIZE[2:0]		
rw								rw	rw	rw	rw	rw	rw	rw	rw
15	14	13	12	11	10	9	8	7	6	5	4	3	2	1	0
ASYNC WAIT	EXT MOD	WAIT EN	WREN	WAIT CFG	Res.	WAIT POL	BURST EN	Res.	FACC EN	MWID[1:0]		MTYP[1:0]		MUX EN	MBK EN
rw	rw	rw	rw	rw		rw	rw		rw	rw	rw	rw	rw	rw	rw

Bit 31 **FMCEN**: FMC controller enable

This bit enables or disables the FMC controller.

0: Disable the FMC controller

1: Enable the FMC controller

Note: The FMCEN bit of the FMC_BCR2..4 registers is don't care. It is only enabled through the FMC_BCR1 register.

Bits 30:24 Reserved, must be kept at reset value.

Bits 23:22 **NBLSET[1:0]:** Byte lane (NBL) setup

These bits configure the NBL setup timing from NBLx low to chip select NEx low.

00: NBL setup time is 0 AHB clock cycle

01: NBL setup time is 1 AHB clock cycle

10: NBL setup time is 2 AHB clock cycles

11: NBL setup time is 3 AHB clock cycles

Bit 21 **WFDIS:** Write FIFO disable

This bit disables the Write FIFO used by the FMC controller.

0: Write FIFO enabled (Default after reset)

1: Write FIFO disabled

Note: The WFDIS bit of the FMC_BCR2..4 registers is don't care. It is only enabled through the FMC_BCR1 register.

Bit 20 **CCLKEN:** Continuous clock enable

This bit enables the FMC_CLK clock output to external memory devices.

0: The FMC_CLK is only generated during the synchronous memory access (read/write transaction). The FMC_CLK clock ratio is specified by the programmed CLKDIV value in the FMC_BCRx register (default after reset).

1: The FMC_CLK is generated continuously during asynchronous and synchronous access. The FMC_CLK clock is activated when the CCLKEN is set.

Note: The CCLKEN bit of the FMC_BCR2..4 registers is don't care. It is only enabled through the FMC_BCR1 register. Bank 1 must be configured in Synchronous mode to generate the FMC_CLK continuous clock.

Note: If CCLKEN bit is set, the FMC_CLK clock ratio is specified by CLKDIV value in the FMC_BTR1 register. CLKDIV in FMC_BWTR1 is don't care.

Note: If the Synchronous mode is used and CCLKEN bit is set, the synchronous memories connected to other banks than Bank 1 are clocked by the same clock (the CLKDIV value in the FMC_BTR2..4 and FMC_BWTR2..4 registers for other banks has no effect.)

Bit 19 **CBURSTRW:** Write burst enable

For PSRAM (CRAM) operating in Burst mode, the bit enables synchronous accesses during write operations. The enable bit for synchronous read accesses is the BURSTEN bit in the FMC_BCRx register.

0: Write operations are always performed in Asynchronous mode.

1: Write operations are performed in Synchronous mode.

Bits 18:16 **CPSIZE[2:0]**: CRAM page size

These are used for CellularRAM™ 1.5 which does not allow burst access to cross the address boundaries between pages. When these bits are configured, the FMC controller splits automatically the burst access when the memory page size is reached (refer to memory datasheet for page size).

000: No burst split when crossing page boundary (default after reset)

001: 128 bytes

010: 256 bytes

011: 512 bytes

100: 1024 bytes

Others: reserved

Bit 15 **ASYNCWAIT**: Wait signal during asynchronous transfers

This bit enables/disables the FMC to use the wait signal even during an asynchronous protocol.

0: NWAIT signal is not taken in to account when running an asynchronous protocol (default after reset).

1: NWAIT signal is taken in to account when running an asynchronous protocol.

Bit 14 **EXTMOD:** Extended mode enable

This bit enables the FMC to program the write timings for non multiplexed asynchronous accesses inside the FMC_BWTR register, thus resulting in different timings for read and write operations.

0: values inside FMC_BWTR register are not taken into account (default after reset)

1: values inside FMC_BWTR register are taken into account

Note: When the Extended mode is disabled, the FMC can operate in mode 1 or mode 2 as follows:

- *Mode 1 is the default mode when the SRAM/PSRAM memory type is selected (MTYP = 0x0 or 0x01)*
- *Mode 2 is the default mode when the NOR memory type is selected (MTYP = 0x10).*

Bit 13 **WAITEN:** Wait enable bit

This bit enables/disables wait-state insertion via the NWAIT signal when accessing the memory in Synchronous mode.

0: NWAIT signal is disabled (its level not taken into account, no wait state inserted after the programmed Flash latency period).

1: NWAIT signal is enabled (its level is taken into account after the programmed latency period to insert wait states if asserted) (default after reset).

Bit 12 **WREN:** Write enable bit

This bit indicates whether write operations are enabled/disabled in the bank by the FMC.

0: Write operations are disabled in the bank by the FMC, an AHB error is reported.

1: Write operations are enabled for the bank by the FMC (default after reset).

Bit 11 **WAITCFG:** Wait timing configuration

The NWAIT signal indicates whether the data from the memory are valid or if a wait state must be inserted when accessing the memory in Synchronous mode. This configuration bit determines if NWAIT is asserted by the memory one clock cycle before the wait state or during the wait state:

0: NWAIT signal is active one data cycle before wait state (default after reset).

1: NWAIT signal is active during wait state (not used for PSRAM).

Bit 10 Reserved, must be kept at reset value.

Bit 9 **WAITPOL:** Wait signal polarity bit

Defines the polarity of the wait signal from memory used for either in Synchronous or Asynchronous mode.

0: NWAIT active low (default after reset)

1: NWAIT active high

Bit 8 **BURSTEN:** Burst enable bit

This bit enables/disables synchronous accesses during read operations. It is valid only for synchronous memories operating in Burst mode.

0: Burst mode disabled (default after reset). Read accesses are performed in Asynchronous mode.

1: Burst mode enable. Read accesses are performed in Synchronous mode.

Bit 7 Reserved, must be kept at reset value.

Bit 6 **FACCEN:** Flash access enable

Enables NOR Flash memory access operations.

0: Corresponding NOR Flash memory access is disabled.

1: Corresponding NOR Flash memory access is enabled (default after reset).

Bits 5:4 **MWID[1:0]:** Memory data bus width

Defines the external memory device width, valid for all type of memories.

00: 8 bits

01: 16 bits (default after reset)

10: reserved

11: reserved

Bits 3:2 **MTYP[1:0]:** Memory type

Defines the type of external memory attached to the corresponding memory bank.

00: SRAM/FRAM (default after reset for Bank 2...4)

01: PSRAM (CRAM) / FRAM

10: NOR Flash/OneNAND Flash (default after reset for Bank 1)

11: reserved

Bit 1 **MUXEN:** Address/data multiplexing enable bit

When this bit is set, the address and data values are multiplexed on the data bus, valid only with NOR and PSRAM memories:

0: Address/data non multiplexed

1: Address/data multiplexed on databus (default after reset)

Bit 0 **MBKEN:** Memory bank enable bit

Enables the memory bank. After reset Bank1 is enabled, all others are disabled. Accessing a disabled bank causes an ERROR on AHB bus.

0: Corresponding memory bank is disabled.

1: Corresponding memory bank is enabled.

SRAM/NOR-Flash chip-select timing register for bank x (FMC_BTRx)

Address offset: 0x04 + 8 * (x – 1), (x = 1 to 4)

Reset value: 0x0FFF FFFF

This register contains the control information of each memory bank, used for SRAMs, PSRAM and NOR Flash memories.If the EXTMOD bit is set in the FMC_BCRx register, then this register is partitioned for write and read access, that is, 2 registers are available: one to configure read accesses (this register) and one to configure write accesses (FMC_BWTRx registers).

31	30	29	28	27	26	25	24	23	22	21	20	19	18	17	16
DATAHLD[1:0]		ACCMOD[1:0]		DATLAT[3:0]				CLKDIV[3:0]				BUSTURN[3:0]			
rw	rw	rw	rw	rw	rw	rw	rw	rw	rw	rw	rw	rw	rw	rw	rw
15	14	13	12	11	10	9	8	7	6	5	4	3	2	1	0
DATAST[7:0]								ADDHLD[3:0]				ADDSET[3:0]			
rw	rw	rw	rw	rw	rw	rw	rw	rw	rw	rw	rw	rw	rw	rw	rw

Bits 31:30 **DATAHLD[1:0]:** Data hold phase duration

These bits are written by software to define the duration of the data hold phase in HCLK cycles (refer to *Figure 108* to *Figure 120*), used in asynchronous accesses:

For read accesses

00: DATAHLD phase duration = 0 × HCLK clock cycle (default)

01: DATAHLD phase duration = 1 × HCLK clock cycle

10: DATAHLD phase duration = 2 × HCLK clock cycle

11: DATAHLD phase duration = 3 × HCLK clock cycle

For write accesses

00: DATAHLD phase duration = 1 × HCLK clock cycle (default)

01: DATAHLD phase duration = 2 × HCLK clock cycle

10: DATAHLD phase duration = 3 × HCLK clock cycle

11: DATAHLD phase duration = 4 × HCLK clock cycle

Bits 29:28 **ACCMOD[1:0]:** Access mode

Specifies the asynchronous access modes as shown in the timing diagrams. These bits are taken into account only when the EXTMOD bit in the FMC_BCRx register is 1.

00: Access mode A

01: Access mode B

10: Access mode C

11: Access mode D

Bits 27:24 **DATLAT[3:0]:** (see note below bit descriptions): Data latency for synchronous memory

For synchronous access with read/write Burst mode enabled (BURSTEN / CBURSTRW bits set), defines the number of memory clock cycles (+2) to issue to the memory before reading/writing the first data:

This timing parameter is not expressed in HCLK periods, but in FMC_CLK periods.

For asynchronous access, this value is don't care.

0000: Data latency of 2 CLK clock cycles for first burst access

1111: Data latency of 17 CLK clock cycles for first burst access (default value after reset)

Bits 23:20 **CLKDIV[3:0]:** Clock divide ratio (for FMC_CLK signal)

Defines the period of FMC_CLK clock output signal, expressed in number of HCLK cycles:

0000: FMC_CLK period= 1x HCLK period

0001: FMC_CLK period = 2 × HCLK periods

0010: FMC_CLK period = 3 × HCLK periods

1111: FMC_CLK period = 16 × HCLK periods (default value after reset)

In asynchronous NOR Flash, SRAM or PSRAM accesses, this value is don't care.

Note: Refer to Section 25.6.5: Synchronous transactions for FMC_CLK divider ratio formula)

Bits 19:16 **BUSTURN[3:0]:** Bus turnaround phase duration

These bits are written by software to add a delay at the end of current read or write transaction to next transaction on the same bank.

This delay allows to match the minimum time between consecutive transactions (t_{EHEL} from NEx high to NEx low) and the maximum time needed by the memory to free the data bus after a read access (t_{EHQZ}, chip enable high to output Hi-Z). This delay is recommended for mode D and muxed mode. For non-muxed memory, the bus turnaround delay can be set to minimum value.

(BUSTURN + 1)HCLK period ≥ max(t_{EHEL} min, t_{EHQZ} max)

For FRAM memories, the bus turnaround delay should be configured to match the minimum tPC (precharge time) timings. The bus turnaround delay is inserted between any consecutive transactions on the same bank (read/read, write/write, read/write and write/read) to match the tPC memory timing. The chip select is toggling between any consecutive accesses.

(BUSTURN + 1)HCLK period ≥ t_{PC} min

0000: BUSTURN phase duration = 1 HCLK clock cycle added

...

1111: BUSTURN phase duration = 16 x HCLK clock cycles added (default value after reset)

Bits 15:8 **DATAST[7:0]:** Data-phase duration

These bits are written by software to define the duration of the data phase (refer to *Figure 108* to *Figure 120*), used in asynchronous accesses:

0000 0000: Reserved

0000 0001: DATAST phase duration = 1 × HCLK clock cycles

0000 0010: DATAST phase duration = 2 × HCLK clock cycles

...

1111 1111: DATAST phase duration = 255 × HCLK clock cycles (default value after reset)

For each memory type and access mode data-phase duration, refer to the respective figure (*Figure 108* to *Figure 120*).

Example: Mode 1, write access, DATAST=1: Data-phase duration= DATAST+1 = 2 HCLK clock cycles.

Note: In synchronous accesses, this value is don't care.

Bits 7:4 **ADDHLD[3:0]:** Address-hold phase duration

These bits are written by software to define the duration of the *address hold* phase (refer to *Figure 108* to *Figure 120*), used in mode D or multiplexed accesses:
0000: Reserved
0001: ADDHLD phase duration =1 × HCLK clock cycle
0010: ADDHLD phase duration = 2 × HCLK clock cycle
...
1111: ADDHLD phase duration = 15 × HCLK clock cycles (default value after reset)
For each access mode address-hold phase duration, refer to the respective figure (*Figure 108* to *Figure 120*).

Note: In synchronous accesses, this value is not used, the address hold phase is always 1 memory clock period duration.

Bits 3:0 **ADDSET[3:0]:** Address setup phase duration

These bits are written by software to define the duration of the *address setup* phase (refer to *Figure 108* to *Figure 120*), used in SRAMs, ROMs, asynchronous NOR Flash and PSRAM:
0000: ADDSET phase duration = 0 × HCLK clock cycle
...
1111: ADDSET phase duration = 15 × HCLK clock cycles (default value after reset)
For each access mode address setup phase duration, refer to the respective figure (*Figure 108* to *Figure 120*).

Note: In synchronous accesses, this value is don't care.
In Muxed mode or mode D, the minimum value for ADDSET is 1.
In mode 1 and PSRAM memory, the minimum value for ADDSET is 1.

Note: PSRAMs (CRAMs) have a variable latency due to internal refresh. Therefore these memories issue the NWAIT signal during the whole latency phase to prolong the latency as needed.
With PSRAMs (CRAMs) the filled DATLAT must be set to 0, so that the FMC exits its latency phase soon and starts sampling NWAIT from memory, then starts to read or write when the memory is ready.
This method can be used also with the latest generation of synchronous Flash memories that issue the NWAIT signal, unlike older Flash memories (check the datasheet of the specific Flash memory being used).

SRAM/NOR-Flash write timing registers x (FMC_BWTRx)

Address offset: 0x104 + 8 * (x – 1), (x = 1 to 4)

Reset value: 0x0FFF FFFF

This register contains the control information of each memory bank. It is used for SRAMs, PSRAMs and NOR Flash memories. When the EXTMOD bit is set in the FMC_BCRx register, then this register is active for write access.

31	30	29	28	27	26	25	24	23	22	21	20	19	18	17	16
DATAHLD[1:0]		ACCMOD[1:0]		Res.	Res.	Res.	Res.	Res.	Res.	Res.	Res.	BUSTURN[3:0]			
rw	rw	rw	rw									rw	rw	rw	rw
15	14	13	12	11	10	9	8	7	6	5	4	3	2	1	0
DATAST[7:0]								ADDHLD[3:0]				ADDSET[3:0]			
rw	rw	rw	rw	rw	rw	rw	rw	rw	rw	rw	rw	rw	rw	rw	rw

Bits 31:30 **DATAHLD[1:0]:** Data hold phase duration

These bits are written by software to define the duration of the data hold phase in HCLK cycles (refer to *Figure 108* to *Figure 120*), used in asynchronous write accesses:
00: DATAHLD phase duration = 1 × HCLK clock cycle (default)
01: DATAHLD phase duration = 2 × HCLK clock cycle
10: DATAHLD phase duration = 3 × HCLK clock cycle
11: DATAHLD phase duration = 4 × HCLK clock cycle

Bits 29:28 **ACCMOD[1:0]:** Access mode.

Specifies the asynchronous access modes as shown in the next timing diagrams.These bits are taken into account only when the EXTMOD bit in the FMC_BCRx register is 1.
00: Access mode A
01: Access mode B
10: Access mode C
11: Access mode D

Bits 27:20 Reserved, must be kept at reset value.

Bits 19:16 **BUSTURN[3:0]**: Bus turnaround phase duration

These bits are written by software to add a delay at the end of current write transaction to next transaction on the same bank.
For FRAM memories, the bus turnaround delay should be configured to match the minimum t_{PC} (precharge time) timings. The bus turnaround delay is inserted between any consecutive transactions on the same bank (read/read, write/write, read/write and write/read). The chip select is toggling between any consecutive accesses.
(BUSTURN + 1)HCLK period ≥ tPC min

0000: BUSTURN phase duration = 1 HCLK clock cycle added
...
1111: BUSTURN phase duration = 16 x HCLK clock cycles added (default value after reset)

Bits 15:8 **DATAST[7:0]:** Data-phase duration.

These bits are written by software to define the duration of the data phase (refer to *Figure 108* to *Figure 120*), used in asynchronous SRAM, PSRAM and NOR Flash memory accesses:
0000 0000: Reserved
0000 0001: DATAST phase duration = 1 × HCLK clock cycles
0000 0010: DATAST phase duration = 2 × HCLK clock cycles
...
1111 1111: DATAST phase duration = 255 × HCLK clock cycles (default value after reset)

Bits 7:4 **ADDHLD[3:0]:** Address-hold phase duration.

These bits are written by software to define the duration of the *address hold* phase (refer to *Figure 117* to *Figure 120*), used in asynchronous multiplexed accesses:
0000: Reserved
0001: ADDHLD phase duration = 1 × HCLK clock cycle
0010: ADDHLD phase duration = 2 × HCLK clock cycle
...
1111: ADDHLD phase duration = 15 × HCLK clock cycles (default value after reset)

Note: In synchronous NOR Flash accesses, this value is not used, the address hold phase is always 1 Flash clock period duration.

Bits 3:0 **ADDSET[3:0]:** Address setup phase duration.

These bits are written by software to define the duration of the *address setup* phase in HCLK cycles (refer to *Figure 108* to *Figure 120*), used in asynchronous accesses:

0000: ADDSET phase duration = 0 × HCLK clock cycle

...

1111: ADDSET phase duration = 15 × HCLK clock cycles (default value after reset)

Note: In synchronous accesses, this value is not used, the address setup phase is always 1 Flash clock period duration. In muxed mode, the minimum ADDSET value is 1.

PSRAM chip select counter register (FMC_PCSCNTR)

Address offset: 0x20

Reset value: 0x0000 0000

This register contains the PSRAM chip select counter value for Synchronous and Asynchronous modes. The chip select counter is common to all banks and can be enabled separately on each bank. During PSRAM read or write accesses, this value is loaded into a timer which is decremented while the NE signal is held low. When the timer reaches 0, the PSRAM controller splits the current access, toggles NE to allow PSRAM device refresh, and restarts a new access. The programmed counter value guarantees a maximum NE pulse width (t_{CEM}) as specified for PSRAM devices. The counter is reloaded and starts decrementing each time a new access is started by a transition of NE from high to low.

31	30	29	28	27	26	25	24	23	22	21	20	19	18	17	16
Res.	Res.	Res.	Res.	Res.	Res.	Res.	Res.	Res.	Res.	Res.	Res.	CNTB4EN	CNTB3EN	CNTB2EN	CNTB1EN
												rw	rw	rw	rw

15	14	13	12	11	10	9	8	7	6	5	4	3	2	1	0
CSCOUNT[15:0]															
rw	rw	rw	rw	rw	rw	rw	rw	rw	rw	rw	rw	rw	rw	rw	rw

Bits 31:20 Reserved, must be kept at reset value.

Bit 19 **CNTB4EN:** Counter Bank 4 enable

This bit enables the chip select counter for PSRAM/NOR Bank 4.

0: Counter disabled for Bank 4

1: Counter enabled for Bank 4

Bit 18 **CNTB3EN:** Counter Bank 3 enable

This bit enables the chip select counter for PSRAM/NOR Bank 3.

0: Counter disabled for Bank 3.

1: Counter enabled for Bank 3

Bit 17 **CNTB2EN:** Counter Bank 2 enable

This bit enables the chip select counter for PSRAM/NOR Bank 2.

0: Counter disabled for Bank 2

1: Counter enabled for Bank 2

Bit 16 **CNTB1EN:** Counter Bank 1 enable

This bit enables the chip select counter for PSRAM/NOR Bank 1.

0: Counter disabled for Bank 1

1: Counter enabled for Bank 1

Bits 15:0 **CSCOUNT[15:0]:** Chip select counter.
These bits are written by software to define the maximum chip select low pulse duration. It is expressed in FMC_CLK cycles for synchronous accesses and in HCLK cycles for asynchronous accesses.
The counter is disabled if the programmed value is 0.

25.7 NAND Flash controller

The FMC generates the appropriate signal timings to drive the following types of device:

- 8- and 16-bit NAND Flash memories

The NAND bank is configured through dedicated registers (*Section 25.7.7*). The programmable memory parameters include access timings (shown in *Table 210*) and ECC configuration.

Table 210. Programmable NAND Flash access parameters

Parameter	Function	Access mode	Unit	Min.	Max.
Memory setup time	Number of clock cycles (HCLK) required to set up the address before the command assertion	Read/Write	AHB clock cycle (HCLK)	1	255
Memory wait	Minimum duration (in HCLK clock cycles) of the command assertion	Read/Write	AHB clock cycle (HCLK)	2	255
Memory hold	Number of clock cycles (HCLK) during which the address must be held (as well as the data if a write access is performed) after the command de-assertion	Read/Write	AHB clock cycle (HCLK)	1	254
Memory databus high-Z	Number of clock cycles (HCLK) during which the data bus is kept in high-Z state after a write access has started	Write	AHB clock cycle (HCLK)	1	255

25.7.1 External memory interface signals

The following tables list the signals that are typically used to interface NAND Flash memory.

Note: The prefix “N” identifies the signals which are active low.

8-bit NAND Flash memory

Table 211. 8-bit NAND Flash

FMC signal name	I/O	Function
A[17]	O	NAND Flash address latch enable (ALE) signal
A[16]	O	NAND Flash command latch enable (CLE) signal
D[7:0]	I/O	8-bit multiplexed, bidirectional address/data bus
NCE	O	Chip select
NOE(= NRE)	O	Output enable (memory signal name: read enable, NRE)

Table 211. 8-bit NAND Flash (continued)

FMC signal name	I/O	Function
NWE	O	Write enable
NWAIT/INT	I	NAND Flash ready/busy input signal to the FMC

Theoretically, there is no capacity limitation as the FMC can manage as many address cycles as needed.

16-bit NAND Flash memory

Table 212. 16-bit NAND Flash

FMC signal name	I/O	Function
A[17]	O	NAND Flash address latch enable (ALE) signal
A[16]	O	NAND Flash command latch enable (CLE) signal
D[15:0]	I/O	16-bit multiplexed, bidirectional address/data bus
NCE	O	Chip select
NOE(= NRE)	O	Output enable (memory signal name: read enable, NRE)
NWE	O	Write enable
NWAIT/INT	I	NAND Flash ready/busy input signal to the FMC

Theoretically, there is no capacity limitation as the FMC can manage as many address cycles as needed.

25.7.2 NAND Flash supported memories and transactions

Table 213 shows the supported devices, access modes and transactions. Transactions not allowed (or not supported) by the NAND Flash controller are shown in gray.

Table 213. Supported memories and transactions

Device	Mode	R/W	AHB data size	Memory data size	Allowed/ not allowed	Comments
NAND 8-bit	Asynchronous	R	8	8	Y	-
	Asynchronous	W	8	8	Y	-
	Asynchronous	R	16	8	Y	Split into 2 FMC accesses
	Asynchronous	W	16	8	Y	Split into 2 FMC accesses
	Asynchronous	R	32	8	Y	Split into 4 FMC accesses
	Asynchronous	W	32	8	Y	Split into 4 FMC accesses

Table 213. Supported memories and transactions (continued)

Device	Mode	R/W	AHB data size	Memory data size	Allowed/ not allowed	Comments
NAND 16-bit	Asynchronous	R	8	16	Y	-
	Asynchronous	W	8	16	N	-
	Asynchronous	R	16	16	Y	-
	Asynchronous	W	16	16	Y	-
	Asynchronous	R	32	16	Y	Split into 2 FMC accesses
	Asynchronous	W	32	16	Y	Split into 2 FMC accesses

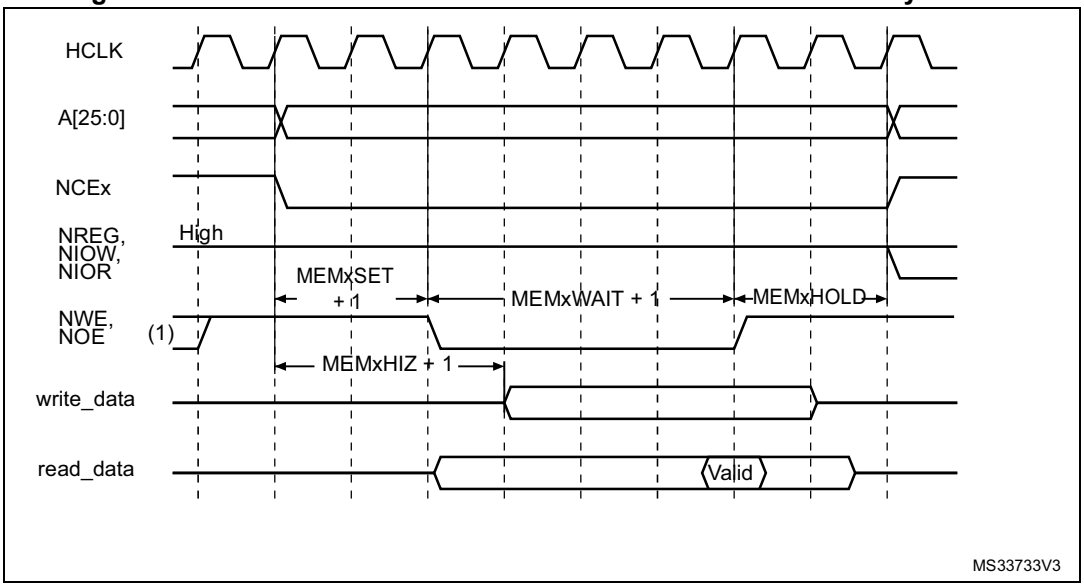
25.7.3 Timing diagrams for NAND Flash memory

The NAND Flash memory bank is managed through a set of registers:

- Control register: FMC_PCR
- Interrupt status register: FMC_SR
- ECC register: FMC_ECCR
- Timing register for Common memory space: FMC_PMEM
- Timing register for Attribute memory space: FMC_PATT

Each timing configuration register contains three parameters used to define number of HCLK cycles for the three phases of any NAND Flash access, plus one parameter that defines the timing for starting driving the data bus when a write access is performed. *Figure 126* shows the timing parameter definitions for common memory accesses, knowing that Attribute memory space access timings are similar.

Figure 126. NAND Flash controller waveforms for common memory access



1. NOE remains high (inactive) during write accesses. NWE remains high (inactive) during read accesses.
2. For write access, the hold phase delay is (MEMHOLD) HCLK cycles and for read access is (MEMHOLD + 2) HCLK cycles.

25.7.4 NAND Flash operations

The command latch enable (CLE) and address latch enable (ALE) signals of the NAND Flash memory device are driven by address signals from the FMC controller. This means that to send a command or an address to the NAND Flash memory, the CPU has to perform a write to a specific address in its memory space.

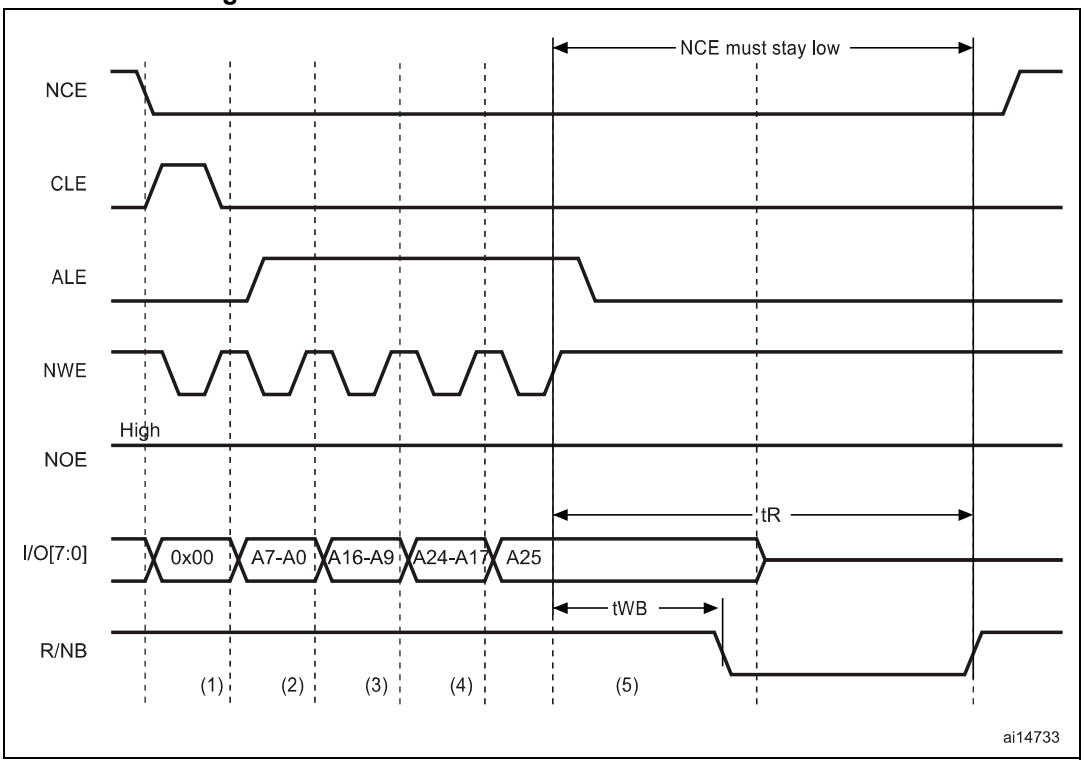
A typical page read operation from the NAND Flash device requires the following steps:

1. Program and enable the corresponding memory bank by configuring the FMC_PCR and FMC_PMEM (and for some devices, FMC_PATT, see *Section 25.7.5: NAND Flash prewait functionality*) registers according to the characteristics of the NAND Flash memory (PWID bits for the data bus width of the NAND Flash, PTYP = 1, PWAITEN = 0 or 1 as needed, see *Section 25.5.2: NAND Flash memory address mapping* for timing configuration).
2. The CPU performs a byte write to the common memory space, with data byte equal to one Flash command byte (for example 0x00 for Samsung NAND Flash devices). The LE input of the NAND Flash memory is active during the write strobe (low pulse on NWE), thus the written byte is interpreted as a command by the NAND Flash memory. Once the command is latched by the memory device, it does not need to be written again for the following page read operations.
3. The CPU can send the start address (STARTAD) for a read operation by writing four bytes (or three for smaller capacity devices), STARTAD[7:0], STARTAD[16:9], STARTAD[24:17] and finally STARTAD[25] (for 64 Mb x 8 bit NAND Flash memories) in the common memory or attribute space. The ALE input of the NAND Flash device is active during the write strobe (low pulse on NWE), thus the written bytes are interpreted as the start address for read operations. Using the attribute memory space makes it possible to use a different timing configuration of the FMC, which can be used to implement the prewait functionality needed by some NAND Flash memories (see details in *Section 25.7.5: NAND Flash prewait functionality*).
4. The controller waits for the NAND Flash memory to be ready (R/NB signal high), before starting a new access to the same or another memory bank. While waiting, the controller holds the NCE signal active (low).
5. The CPU can then perform byte read operations from the common memory space to read the NAND Flash page (data field + Spare field) byte by byte.
6. The next NAND Flash page can be read without any CPU command or address write operation. This can be done in three different ways:
   - by simply performing the operation described in step 5
   - a new random address can be accessed by restarting the operation at step 3
   - a new command can be sent to the NAND Flash device by restarting at step 2

25.7.5 NAND Flash prewait functionality

Some NAND Flash devices require that, after writing the last part of the address, the controller waits for the R/NB signal to go low. (see *Figure 127*).

Figure 127. Access to non 'CE don't care' NAND-Flash



1. CPU wrote byte 0x00 at address 0x7001 0000.
2. CPU wrote byte A7~A0 at address 0x7002 0000.
3. CPU wrote byte A16~A9 at address 0x7002 0000.
4. CPU wrote byte A24~A17 at address 0x7002 0000.
5. CPU wrote byte A25 at address 0x7802 0000: FMC performs a write access using FMC_PATT timing definition, where ATTHOLD ≥ 7 (providing that (7+1) × HCLK = 112 ns > t_{WB} max). This guarantees that NCE remains low until R/NB goes low and high again (only requested for NAND Flash memories where NCE is not don't care).

When this functionality is required, it can be ensured by programming the MEMHOLD value to meet the t_{WB} timing. However any CPU read access to the NAND Flash memory has a hold delay of (MEMHOLD + 2) HCLK cycles and CPU write access has a hold delay of (MEMHOLD) HCLK cycles inserted between the rising edge of the NWE signal and the next access.

To cope with this timing constraint, the attribute memory space can be used by programming its timing register with an ATTHOLD value that meets the t_{WB} timing, and by keeping the MEMHOLD value at its minimum value. The CPU must then use the common memory space for all NAND Flash read and write accesses, except when writing the last address byte to the NAND Flash device, where the CPU must write to the attribute memory space.

25.7.6 Computation of the error correction code (ECC) in NAND Flash memory

The FMC NAND Card controller includes two error correction code computation hardware blocks, one per memory bank. They reduce the host CPU workload when processing the ECC by software.

These two ECC blocks are identical and associated with Bank 2 and Bank 3. As a consequence, no hardware ECC computation is available for memories connected to Bank 4.

The ECC algorithm implemented in the FMC can perform 1-bit error correction and 2-bit error detection per 256, 512, 1 024, 2 048, 4 096 or 8 192 bytes read or written from/to the NAND Flash memory. It is based on the Hamming coding algorithm and consists in calculating the row and column parity.

The ECC modules monitor the NAND Flash data bus and read/write signals (NCE and NWE) each time the NAND Flash memory bank is active.

The ECC operates as follows:

- When accessing NAND Flash memory bank 2 or bank 3, the data present on the D[15:0] bus is latched and used for ECC computation.
- When accessing any other address in NAND Flash memory, the ECC logic is idle, and does not perform any operation. As a result, write operations to define commands or addresses to the NAND Flash memory are not taken into account for ECC computation.

Once the desired number of bytes has been read/written from/to the NAND Flash memory by the host CPU, the FMC_ECCR registers must be read to retrieve the computed value. Once read, they should be cleared by resetting the ECCEN bit to ‘0’. To compute a new data block, the ECCEN bit must be set to one in the FMC_PCR registers.

To perform an ECC computation:

1. Enable the ECCEN bit in the FMC_PCR register.
2. Write data to the NAND Flash memory page. While the NAND page is written, the ECC block computes the ECC value.
3. Read the ECC value available in the FMC_ECCR register and store it in a variable.
4. Clear the ECCEN bit and then enable it in the FMC_PCR register before reading back the written data from the NAND page. While the NAND page is read, the ECC block computes the ECC value.
5. Read the new ECC value available in the FMC_ECCR register.
6. If the two ECC values are the same, no correction is required, otherwise there is an ECC error and the software correction routine returns information on whether the error can be corrected or not.

25.7.7 NAND Flash controller registers

NAND Flash control registers (FMC_PCR)

Address offset: 0x80

Reset value: 0x0000 0018

31	30	29	28	27	26	25	24	23	22	21	20	19	18	17	16
Res.	Res.	Res.	Res.	Res.	Res.	Res.	Res.	Res.	Res.	Res.	Res.	ECCPS[2:0]			TAR3
												rw	rw	rw	rw

15	14	13	12	11	10	9	8	7	6	5	4	3	2	1	0
TAR[2:0]			TCLR[3:0]				Res.	Res.	ECCEN	PWID[1:0]		PTYP	PBKEN	PWAITEN	Res.
rw	rw	rw	rw	rw	rw	rw			rw	rw	rw	rw	rw	rw	

Bits 31:20 Reserved, must be kept at reset value.

Bits 19:17 **ECCPS[2:0]:** ECC page size
Defines the page size for the extended ECC:
000: 256 bytes
001: 512 bytes
010: 1024 bytes
011: 2048 bytes
100: 4096 bytes
101: 8192 bytes

Bits 16:13 **TAR[3:0]:** ALE to RE delay
Sets time from ALE low to RE low in number of AHB clock cycles (HCLK).
Time is: t_ar = (TAR + SET + 2) × THCLK where THCLK is the HCLK clock period
0000: 1 HCLK cycle (default)
1111: 16 HCLK cycles
Note: SET is MEMSET or ATTSET according to the addressed space.

Bits 12:9 **TCLR[3:0]:** CLE to RE delay
Sets time from CLE low to RE low in number of AHB clock cycles (HCLK).
Time is t_clr = (TCLR + SET + 2) × THCLK where THCLK is the HCLK clock period
0000: 1 HCLK cycle (default)
1111: 16 HCLK cycles
Note: SET is MEMSET or ATTSET according to the addressed space.

Bits 8:7 Reserved, must be kept at reset value.

Bit 6 **ECCEN:** ECC computation logic enable bit
0: ECC logic is disabled and reset (default after reset),
1: ECC logic is enabled.

Bits 5:4 **PWID[1:0]:** Data bus width
Defines the external memory device width.
00: 8 bits
01: 16 bits (default after reset).
10: reserved.
11: reserved.

Bit 3 **PTYP:** Memory type
Defines the type of device attached to the corresponding memory bank:
0: Reserved, must be kept at reset value
1: NAND Flash (default after reset)

Bit 2 **PBKEN:** NAND Flash memory bank enable bit
Enables the memory bank. Accessing a disabled memory bank causes an ERROR on AHB bus
0: Corresponding memory bank is disabled (default after reset)
1: Corresponding memory bank is enabled

Bit 1 **PWAITEN:** Wait feature enable bit
Enables the Wait feature for the NAND Flash memory bank:
0: disabled
1: enabled

Bit 0 Reserved, must be kept at reset value.

FIFO status and interrupt register (FMC_SR)

Address offset: 0x84

Reset value: 0x0000 0040

This register contains information about the FIFO status and interrupt. The FMC features a FIFO that is used when writing to memories to transfer up to 16 words of data from the AHB.

This is used to quickly write to the FIFO and free the AHB for transactions to peripherals other than the FMC, while the FMC is draining its FIFO into the memory. One of these register bits indicates the status of the FIFO, for ECC purposes.

The ECC is calculated while the data are written to the memory. To read the correct ECC, the software must consequently wait until the FIFO is empty.

31	30	29	28	27	26	25	24	23	22	21	20	19	18	17	16
Res.	Res.	Res.	Res.	Res.	Res.	Res.	Res.	Res.	Res.	Res.	Res.	Res.	Res.	Res.	Res.
15	14	13	12	11	10	9	8	7	6	5	4	3	2	1	0
Res.	Res.	Res.	Res.	Res.	Res.	Res.	Res.	Res.	FEMPT	IFEN	ILEN	IREN	IFS	ILS	IRS
									r	rw	rw	rw	rw	rw	rw

Bits 31:7 Reserved, must be kept at reset value.

Bit 6 **FEMPT:** FIFO empty

Read-only bit that provides the status of the FIFO

0: FIFO not empty

1: FIFO empty

Bit 5 **IFEN:** Interrupt falling edge detection enable bit

0: Interrupt falling edge detection request disabled

1: Interrupt falling edge detection request enabled

Bit 4 **ILEN:** Interrupt high-level detection enable bit

0: Interrupt high-level detection request disabled

1: Interrupt high-level detection request enabled

Bit 3 **IREN:** Interrupt rising edge detection enable bit

0: Interrupt rising edge detection request disabled

1: Interrupt rising edge detection request enabled

Bit 2 **IFS:** Interrupt falling edge status

The flag is set by hardware and reset by software.

0: No interrupt falling edge occurred

1: Interrupt falling edge occurred

Note: If this bit is written by software to 1 it is set.

Bit 1 **ILS:** Interrupt high-level status

The flag is set by hardware and reset by software.

0: No Interrupt high-level occurred

1: Interrupt high-level occurred

Bit 0 **IRS:** Interrupt rising edge status

The flag is set by hardware and reset by software.

0: No interrupt rising edge occurred

1: Interrupt rising edge occurred

Note: If this bit is written by software to 1 it is set.

Common memory space timing register (FMC_PMEM)

Address offset: Address: 0x88

Reset value: 0xFCFC FCFC

The FMC_PMEM read/write register contains the timing information for NAND Flash memory bank. This information is used to access either the common memory space of the NAND Flash for command, address write access and data read/write access.

31	30	29	28	27	26	25	24	23	22	21	20	19	18	17	16
MEMHIZ[7:0]								MEMHOLD[7:0]							
rw	rw	rw	rw	rw	rw	rw	rw	rw	rw	rw	rw	rw	rw	rw	rw
15	14	13	12	11	10	9	8	7	6	5	4	3	2	1	0
MEMWAIT[7:0]								MEMSET[7:0]							
rw	rw	rw	rw	rw	rw	rw	rw	rw	rw	rw	rw	rw	rw	rw	rw

Bits 31:24 **MEMHIZ[7:0]:** Common memory x data bus Hi-Z time

Defines the number of HCLK clock cycles during which the data bus is kept Hi-Z after the start of a NAND Flash write access to common memory space on socket. This is only valid for write transactions:

0000 0000: 1 HCLK cycle

1111 1110: 255 HCLK cycles

1111 1111: reserved.

Bits 23:16 **MEMHOLD[7:0]:** Common memory hold time

Defines the number of HCLK clock cycles for write access and HCLK (+2) clock cycles for read access during which the address is held (and data for write accesses) after the command is deasserted (NWE, NOE), for NAND Flash read or write access to common memory space on socket x:

0000 0000: reserved.

0000 0001: 1 HCLK cycle for write access / 3 HCLK cycles for read access

1111 1110: 254 HCLK cycles for write access / 256 HCLK cycles for read access

1111 1111: reserved.

Bits 15:8 **MEMWAIT[7:0]:** Common memory wait time

Defines the minimum number of HCLK (+1) clock cycles to assert the command (NWE, NOE), for NAND Flash read or write access to common memory space on socket. The duration of command assertion is extended if the wait signal (NWAIT) is active (low) at the end of the programmed value of HCLK:

0000 0000: reserved

0000 0001: 2HCLK cycles (+ wait cycle introduced by deasserting NWAIT)

1111 1110: 255 HCLK cycles (+ wait cycle introduced by deasserting NWAIT)

1111 1111: reserved.

Bits 7:0 **MEMSET[7:0]:** Common memory x setup time

Defines the number of HCLK (+1) clock cycles to set up the address before the command assertion (NWE, NOE), for NAND Flash read or write access to common memory space on socket x:

0000 0000: 1 HCLK cycle

1111 1110: 255 HCLK cycles

1111 1111: reserved

Attribute memory space timing register (FMC_PATT)

Address offset: 0x8C

Reset value: 0xFCFC FCFC

The FMC_PATT read/write register contains the timing information for NAND Flash memory bank. It is used for 8-bit accesses to the attribute memory space of the NAND Flash for the last address write access if the timing must differ from that of previous accesses (for Ready/Busy management, refer to *Section 25.7.5: NAND Flash prewait functionality*).

31	30	29	28	27	26	25	24	23	22	21	20	19	18	17	16
ATTHIZ[7:0]								ATTHOLD[7:0]							
rw	rw	rw	rw	rw	rw	rw	rw	rw	rw	rw	rw	rw	rw	rw	rw
15	14	13	12	11	10	9	8	7	6	5	4	3	2	1	0
ATTWAIT[7:0]								ATTSET[7:0]							
rw	rw	rw	rw	rw	rw	rw	rw	rw	rw	rw	rw	rw	rw	rw	rw

Bits 31:24 **ATTHIZ[7:0]:** Attribute memory data bus Hi-Z time

Defines the number of HCLK clock cycles during which the data bus is kept in Hi-Z after the start of a NAND Flash write access to attribute memory space on socket. Only valid for writ transaction:

0000 0000: 0 HCLK cycle

1111 1110: 255 HCLK cycles

1111 1111: reserved.

Bits 23:16 **ATTHOLD[7:0]:** Attribute memory hold time

Defines the number of HCLK clock cycles for write access and HCLK (+2) clock cycles for read access during which the address is held (and data for write access) after the command deassertion (NWE, NOE), for NAND Flash read or write access to attribute memory space on socket:

0000 0000: reserved

0000 0001: 1 HCLK cycle for write access / 3 HCLK cycles for read access

1111 1110: 254 HCLK cycles for write access / 256 HCLK cycles for read access

1111 1111: reserved.

Bits 15:8 **ATTWAIT[7:0]:** Attribute memory wait time

Defines the minimum number of HCLK (+1) clock cycles to assert the command (NWE, NOE), for NAND Flash read or write access to attribute memory space on socket x. The duration for command assertion is extended if the wait signal (NWAIT) is active (low) at the end of the programmed value of HCLK:

0000 0000: reserved

0000 0001: 2 HCLK cycles (+ wait cycle introduced by deassertion of NWAIT)

1111 1110: 255 HCLK cycles (+ wait cycle introduced by deasserting NWAIT)

1111 1111: reserved.

Bits 7:0 **ATTSET[7:0]:** Attribute memory setup time

Defines the number of HCLK (+1) clock cycles to set up address before the command assertion (NWE, NOE), for NAND Flash read or write access to attribute memory space on socket:
0000 0000: 1 HCLK cycle
1111 1110: 255 HCLK cycles
1111 1111: reserved.

ECC result registers (FMC_ECCR)

Address offset: 0x94

Reset value: 0x0000 0000

This register contain the current error correction code value computed by the ECC computation modules of the FMC NAND controller. When the CPU reads the data from a NAND Flash memory page at the correct address (refer to *Section 25.7.6: Computation of the error correction code (ECC) in NAND Flash memory*), the data read/written from/to the NAND Flash memory are processed automatically by the ECC computation module. When X bytes have been read (according to the ECCPS field in the FMC_PCR registers), the CPU must read the computed ECC value from the FMC_ECC registers. It then verifies if these computed parity data are the same as the parity value recorded in the spare area, to determine whether a page is valid, and, to correct it otherwise. The FMC_ECCR register should be cleared after being read by setting the ECCEN bit to 0. To compute a new data block, the ECCEN bit must be set to 1.

31	30	29	28	27	26	25	24	23	22	21	20	19	18	17	16
ECC[31:16]															
r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r
15	14	13	12	11	10	9	8	7	6	5	4	3	2	1	0
ECC[15:0]															
r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r

Bits 31:0 **ECC[31:0]:** ECC result

This field contains the value computed by the ECC computation logic. *Table 214* describes the contents of these bitfields.

Table 214. ECC result relevant bits

ECCPS[2:0]	Page size in bytes	ECC bits
000	256	ECC[21:0]
001	512	ECC[23:0]
010	1024	ECC[25:0]
011	2048	ECC[27:0]
100	4096	ECC[29:0]
101	8192	ECC[31:0]

25.7.8 FMC register map

Table 215. FMC register map and reset values

Offset	Register	31	30	29	28	27	26	25	24	23	22	21	20	19	18	17	16	15	14	13	12	11	10	9	8	7	6	5	4	3	2	1	0
0x00	**FMC_BCR1**	FMCEN	Res.	Res.	Res.	Res.	Res.	Res.	Res.	NBL SET [1:0]		WFDIS	CCLKEN	CBURSTRW	CPSIZE [2:0]			ASYNCWAIT	EXTMOD	WAITEN	WREN	WAITCFG	Res.	WAITPOL	BURSTEN	Res.	FACCEN	MWID [1:0]		MTYP [1:0]		MUXEN	MBKEN
	Reset value	0								0	0	0	0	0	0	0	0	0	0	1	1	0		0	0		1	0	1	1	0	1	1
0x08	**FMC_BCR2**	FMCEN	Res.	Res.	Res.	Res.	Res.	Res.	Res.	NBL SET [1:0]		Res.	Res.	CBURSTRW	CPSIZE [2:0]			ASYNCWAIT	EXTMOD	WAITEN	WREN	WAITCFG	Res.	WAITPOL	BURSTEN	Res.	FACCEN	MWID [1:0]		MTYP [1:0]		MUXEN	MBKEN
	Reset value	0								0	0			0	0	0	0	0	0	1	1	0		0	0		1	0	1	0	0	1	0
0x10	**FMC_BCR3**	FMCEN	Res.	Res.	Res.	Res.	Res.	Res.	Res.	NBL SET [1:0]		Res.	Res.	CBURSTRW	CPSIZE [2:0]			ASYNCWAIT	EXTMOD	WAITEN	WREN	WAITCFG	Res.	WAITPOL	BURSTEN	Res.	FACCEN	MWID [1:0]		MTYP [1:0]		MUXEN	MBKEN
	Reset value	0								0	0			0	0	0	0	0	0	1	1	0		0	0		1	0	1	0	0	1	0
0x18	**FMC_BCR4**	FMCEN	Res.	Res.	Res.	Res.	Res.	Res.	Res.	NBL SET [1:0]		Res.	Res.	CBURSTRW	CPSIZE [2:0]			ASYNCWAIT	EXTMOD	WAITEN	WREN	WAITCFG	Res.	WAITPOL	BURSTEN	Res.	FACCEN	MWID [1:0]		MTYP [1:0]		MUXEN	MBKEN
	Reset value	0								0	0			0	0	0	0	0	0	1	1	0		0	0		1	0	1	0	0	1	0
0x04	**FMC_BTR1**	DATAHLD[1:0]		ACCMOD[1:0]		DATLAT[3:0]				CLKDIV[3:0]				BUSTURN [3:0]				DATAST[7:0]								ADDHLD[3:0]				ADDSET[3:0]			
	Reset value	0	0	0	0	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1
0x0C	**FMC_BTR2**	DATAHLD[1:0]		ACCMOD[1:0]		DATLAT[3:0]				CLKDIV[3:0]				BUSTURN [3:0]				DATAST[7:0]								ADDHLD[3:0]				ADDSET[3:0]			
	Reset value	0	0	0	0	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1
0x14	**FMC_BTR3**	DATAHLD[1:0]		ACCMOD[1:0]		DATLAT[3:0]				CLKDIV[3:0]				BUSTURN [3:0]				DATAST[7:0]								ADDHLD[3:0]				ADDSET[3:0]			
	Reset value	0	0	0	0	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1
0x1C	**FMC_BTR4**	DATAHLD[1:0]		ACCMOD[1:0]		DATLAT[3:0]				CLKDIV[3:0]				BUSTURN [3:0]				DATAST[7:0]								ADDHLD[3:0]				ADDSET[3:0]			
	Reset value	0	0	0	0	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1
0x20	**FMC_ PCSCNTR**	Res.	Res.	Res.	Res.	Res.	Res.	Res.	Res.	Res.	Res.	Res.	Res.	CNTB4EN	CNTB3EN	CNTB2EN	CNTB1EN	CSCOUNT[15:0]															
	Reset value													0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0
0x104	**FMC_BWTR1**	DATAHLD[1:0]		ACCMOD[1:0]		Res.	Res.	Res.	Res.	Res.	Res.	Res.	Res.	BUSTURN [3:0]				DATAST[7:0]								ADDHLD[3:0]				ADDSET[3:0]			
	Reset value	0	0	0	0									1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1

Table 215. FMC register map and reset values (continued)

Offset	Register	31	30	29	28	27	26	25	24	23	22	21	20	19	18	17	16	15	14	13	12	11	10	9	8	7	6	5	4	3	2	1	0
0x10C	**FMC_BWTR2**	DATAHLD[1:0]		ACCMOD[1:0]		Res.	Res.	Res.	Res.	Res.	Res.	Res.	Res.	BUSTURN [3:0]				DATAST[7:0]								ADDHLD[3:0]				ADDSET[3:0]			
	Reset value	0	0	0	0									1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1
0x114	**FMC_BWTR3**	DATAHLD[1:0]		ACCMOD[1:0]		Res.	Res.	Res.	Res.	Res.	Res.	Res.	Res.	BUSTURN [3:0]				DATAST[7:0]								ADDHLD[3:0]				ADDSET[3:0]			
	Reset value	0	0	0	0									1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1
0x11C	**FMC_BWTR4**	DATAHLD[1:0]		ACCMOD[1:0]		Res.	Res.	Res.	Res.	Res.	Res.	Res.	Res.	BUSTURN [3:0]				DATAST[7:0]								ADDHLD[3:0]				ADDSET[3:0]			
	Reset value	0	0	0	0									1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1
0x80	**FMC_PCR**	Res.	Res.	Res.	Res.	Res.	Res.	Res.	Res.	Res.	Res.	Res.	Res.	ECCPS [2:0]				TAR[3:0]				TCLR[3:0]				Res.	Res.	ECCEN	PWID [1:0]		PTYP	PBKEN	PWAITEN	Res.
	Reset value													0	0	0	0	0	0	0	0	0	0	0			0	0	1	1	0	0	
0x84	**FMC_SR**	Res.	Res.	Res.	Res.	Res.	Res.	Res.	Res.	Res.	Res.	Res.	Res.	Res.	Res.	Res.	Res.	Res.	Res.	Res.	Res.	Res.	Res.	Res.	Res.	Res.	FEMPT	IFEN	ILEN	IREN	IFS	ILS	IRS
	Reset value																										1	0	0	0	0	0	0
0x88	**FMC_PMEM**	MEMHIZx[7:0]								MEMHOLDx[7:0]								MEMWAITx[7:0]								MEMSETx[7:0]							
	Reset value	1	1	1	1	1	1	0	0	1	1	1	1	1	1	0	0	1	1	1	1	1	1	0	0	1	1	1	1	1	1	0	0
0x8C	**FMC_PATT**	ATTHIZ[7:0]								ATTHOLD[7:0]								ATTWAIT[7:0]								ATTSET[7:0]							
	Reset value	1	1	1	1	1	1	0	0	1	1	1	1	1	1	0	0	1	1	1	1	1	1	0	0	1	1	1	1	1	1	0	0
0x94	**FMC_ECCR**	ECCx[31:0]																															
	Reset value	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0

Refer to *Section 2.3 on page 116* for the register boundary addresses.